

PCTEST ENGINEERING LABORATORY, INC.

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HEARING AID COMPATIBILITY

Applicant Name:

Samsung Electronics Co., Ltd. 129, Samsung-ro, Maetan dong, Yeongtong-gu, Suwon-si Gyeonggi-do 16677, Korea Date of Testing: 04/09/2018 - 04/13/2018 Test Site/Location: PCTEST Lab, Columbia, MD, USA Test Report Serial No.: 1M1803190049-09-R1.A3L

FCC ID: A3LSMJ337V

APPLICANT: SAMSUNG ELECTRONICS CO., LTD.

Scope of Test: RF Emissions Testing

Application Type: Certification
FCC Rule Part(s): CFR §20.19(b)
HAC Standard: ANSI C63.19-2011

CTIA Test Plan for Hearing Aid Compatibility Rev 3.1, February 2017

285076 D01 HAC Guidance v05

285076 D02 T-Coil testing for CMRS IP v03

DUT Type: Portable Handset

Model: SM-J337V, SM-J337VPP

Test Device Serial No.: Pre-Production Sample [S/N: 18253]

C63.19-2011 HAC Category: M3 (RF EMISSIONS CATEGORY)

Note: This revised Test Report (S/N: 1M1803190049-09-R1.A3L) supersedes and replaces the previously issued test report on the same subject device for the same type of testing as indicated. Please discard or destroy the previously issued test report(s) and dispose of it accordingly.

This wireless portable device has been shown to be hearing-aid compatible under the above rated category, specified in ANSI/IEEE Std. C63.19-2011 and has been tested in accordance with the specified measurement procedures. Hearing-Aid Compatibility is based on the assumption that all production units will be designed electrically identical to the device tested in this report. Test results reported herein relate only to the item(s) tested. North America bands only.

I attest to the accuracy of data. All measurements reported herein were performed by me or were made under my supervision and are correct to the best of my knowledge and belief. I assume full responsibility for the completeness of these measurements and vouch for the qualifications of all persons taking them.







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Randy Ortanez President

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1. INTRODUCTION

On July 10, 2003, the Federal Communications Commission (FCC) adopted new rules requiring wireless manufacturers and service providers to provide digital wireless phones that are compatible with hearing aids. The FCC has modified the exemption for wireless phones under the Hearing Aid Compatibility Act of 1998 (HAC Act) in WT Docket 01-309 RM-86581 to extend the benefits of wireless telecommunications to individuals with hearing disabilities. These benefits encompass business, social and emergency communications, which increase the value of the wireless network for everyone. An estimated more than 10% of the population in the United States show signs of hearing impairment and of that fraction, almost 80% use hearing aids. Approximately 500 million people worldwide suffer from hearing loss.

Compatibility Tests Involved:

The standard calls for wireless communications devices to be measured for:

- RF Electric-field emissions
- T-coil mode, magnetic-signal strength in the audio band
- T-coil mode, magnetic-signal frequency response through the audio band
- T-coil mode, magnetic-signal and noise articulation index

The hearing aid must be measured for:

- RF immunity in microphone mode
- RF immunity in T-coil mode

In the following tests and results, this report includes the evaluation for a wireless communications device.



Figure 1-1 Hearing Aid in-vitu

¹ FCC Rule & Order, WT Docket 01-309 RM-8658

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2. **DUT DESCRIPTION**



FCC ID: A3LSMJ337V

Manufacturer: Samsung Electronics Co., Ltd.

129, Samsung-ro, Maetan dong,

Yeongtong-gu, Suwon-si Gyeonggi-do 16677, Korea

Model: SM-J337V, SM-J337VPP

Serial Number: 18253

Antenna Configurations: Internal Antenna DUT Type: Portable Handset

Power Reduction for WIFI

This device uses an independent fixed level power reduction mechanism for all WIFI operations during voice or VoIP held to ear scenarios. Reduced powers were used to evaluate for low-power exemption in Section 9.II for WIFI. Detailed descriptions of the power reduction mechanism are included in the operational description.

II. Power Reduction for Licensed Modes

This device uses an independent fixed level power reduction mechanism for CDMA BC0/1, GSM1900, UMTS II, and LTE B2/4 during voice or VoIP held to ear scenarios. Reduced powers were used to evaluate for low-power exemption in Section 9.II for these modes. Detailed descriptions of the power reduction mechanism are included in the operational description.

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Table 2-1 A3LSMJ337V HAC Air Interfaces

Air-Interface	Band (MHz)	Type Transport	HAC Tested	Simultaneous But Not Tested	Name of Voice Service		
	835	VO	Yes	Yes: WIFI or BT	CMRS Voice		
CDMA	1900	VO	163	res. Will Of B1	CIVINS VOICE		
	EvDO	VD	No ¹	Yes: WIFI or BT	Google Duo		
	850	VO	Yes	Yes: WIFI or BT	CMRS Voice		
GSM	1900	VO	res	res. Wiri of Bi	CIVIKS VOICE		
	GPRS/EDGE	VD	No ¹	Yes: WIFI or BT	Google Duo		
UMTS	850	- VD	No ¹	Yes: WIFI or BT	CMRS Voice		
	1900		INO	res. Will Of B1	CIVINS VOICE		
	HSPA	VD	No ¹	Yes: WIFI or BT	Google Duo		
	780 (B13)	VD					
	850 (B5)		No ¹	Yes: WIFI or BT	VoLTE, Google Duo		
LTE (FDD)	1700 (B4)						
	1900 (B2)						
	2500 (B7)						
	2450						
	5200 (U-NII 1)						
WIFI	5300 (U-NII 2A)	VD	No ¹	Yes: CDMA, GSM, UMTS, or LTE	VoWIFI, Google Duo		
	5500 (U-NII 2C)	ı					
	5800 (U-NII 3)						
BT	2450	DT	No	Yes: CDMA, GSM, UMTS, or LTE	N/A		
Type Transport			Notes:	·	_		

VO = Voice Only DT = Digital Data - Not intended for CMRS Service

VD = CMRS and IP Voice over Data Transport

1. Evaluated for MIF and low-power exemption.

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ANSI/IEEE C63.19 PERFORMANCE CATEGORIES 3.

I. RF EMISSIONS

The ANSI Standard presents performance requirements for acceptable interoperability of hearing aids with wireless communications devices. When these parameters are met, a hearing aid operates acceptably in close proximity to a wireless communications device.

Category	Telephone RF Parameters			
Near field Category	E-field emissions CW dB(V/m)			
f < 960 MHz				
M1	50 to 55			
M2	45 to 50			
M3	40 to 45			
M4	< 40			
	f > 960 MHz			
M1	40 to 45			
M2	35 to 40			
M3	30 to 35			
M4	< 30			
Table 3-1 WD near-field categories as defined in ANSI C63.19-2011				

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4. SYSTEM SPECIFICATIONS

ER3DV6 E-Field Probe Description

Construction: One dipole parallel, two dipoles normal to probe axis

Built-in shielding against static charges

Calibration: In air from 100 MHz to 3.0 GHz

(absolute accuracy ±6.0%, k=2)

Frequency: 100 MHz to > 6 GHz;

Linearity: ± 0.2 dB (100 MHz to 3 GHz)

Directivity ± 0.2 dB in air (rotation around probe axis)

± 0.4 dB in air (rotation normal to probe axis)

Dynamic Range 2 V/m to > 1000 V/m

(M3 or better device readings fall well below diode

compression point)

Linearity: ± 0.2 dB

Dimensions Overall length: 330 mm (Tip: 16 mm)

Tip diameter: 8 mm (Body: 12 mm)

Distance from probe tip to dipole centers: 2.5 mm



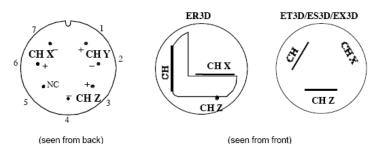
Figure 4-1
E-field Free-space
Probe

Probe Tip Description

HAC field measurements take place in the close near field with high gradients. Increasing the measuring distance from the source will generally decrease the measured field values (in case of the validation dipole approx. 10% per mm).

The electric field probes have an irregular internal geometry because it is physically not possible to have the 3 orthogonal sensors situated with the same center. The effect of the different sensor centers is accounted for in the HAC uncertainty budget ("sensor displacement"). Their geometric center is at 2.5mm from the tip, and the element ends are 1.1mm closer to the tip.

Connector Plan



The antistatic shielding inside the probe is connected to the probe connector case.

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Instrumentation Chain

Equation 1

Conversion of Connector Voltage u, to E-Field E,

$$E_i = \sqrt{\frac{u_i + (u_i^2 \cdot CF)/(DCP)}{Norm_i \cdot ConvF}}$$

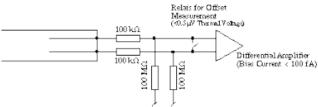
whereby

Eı: electric field in V/m

voltage of channel i at the connector in µV Uí. sensitivity of channel i in µV/(V/m)2 Norm: ConvF: enhancement factor in liquid (ConvF=1 for Air) DCP: diode compression point in µV

CF. signal crest factor (peak power/average power)

Conditions of Calibration



- a lower input impedance of the amplifier will result in different sensitivity factors Norm; and DCP
- larger bias currents will cause higher offset

Probe Response to Frequency

The E-field sensors have inherently a very flat frequency response. They are calibrated with a number of frequencies resulting in a common calibration factor, with the frequency behavior documented in the calibration certificate (See also below). Frequency Response of E-Field

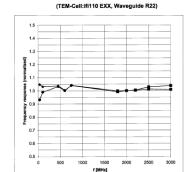


Figure 4-2 E-Field Probe Frequency Response

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SPEAG Robotic System

E-field measurements are performed using the DASY5 automated dosimetric assessment system. The DASY5 is made by Schmid & Partner Engineering AG (SPEAG) in Zurich, Switzerland and consists of high precision robotics system (Staubli), robot controller, Intel CORE i7 computer, nearfield probe, probe alignment sensor, and the HAC phantom. The robot is a six-axis industrial robot performing precise movements to position the probe to the location (points) of maximum electromagnetic field (EMF).



Figure 4-3 SPEAG Robotic System

System Hardware

A cell controller system contains the power supply, robot controller, teach pendant (Joystick), and a remote control used to drive the robot motors. The PC consists of the computer with operating system and RF Measurement Software DASY5 v52.8 (with HAC Extension), A/D interface card, monitor, mouse, and keyboard. The Staubli Robot is connected to the cell controller to allow software manipulation of the robot. A data acquisition electronic (DAE) circuit that performs the signal amplification, signal multiplexing, AD-conversion, offset measurements, mechanical surface detection, collision detection, etc. is connected to the Electro-optical coupler (EOC). The EOC performs the conversion from the optical into digital electric signal of the DAE and transfers data to the PC plug-in card.

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System Electronics

The DAE consists of a highly sensitive electrometer-grade preamplifier with auto-zeroing, a channel and gain-switching multiplexer, a fast 16 bit AD-converter and a command decoder and control logic unit. Transmission to the PC-card is accomplished through an optical downlink for data and status information and an optical uplink for commands and clock lines. The mechanical probe mounting device includes two different sensor systems for frontal and sidewise probe contacts. They are also used for mechanical surface detection and probe collision detection. The robot uses its own controller with a built in VME-bus computer.

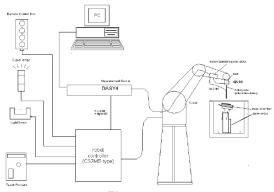


Figure 4-4 SPEAG Robotic System Diagram

DASY5 Instrumentation Chain

The first step of the evaluation is a linearization of the filtered input signal to account for the compression characteristics of the detector diode. The compensation depends on the input signal, the diode type and the DC-transmission factor from the diode to the evaluation electronics. If the exciting field is pulsed, the crest factor of the signal must be known to correctly compensate for peak power. The formula for each channel can be given as:

$$V_i = U_i + U_i^2 \cdot \frac{cf}{dcp_i}$$

= compensated signal of channel i (i = x, y, z)with V_i = input signal of channel i (i = x, y, z)= crest factor of exciting field (DASY parameter) (DASY parameter) dcp_i = diode compression point

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From the compensated input signals the primary field data for each channel can be evaluated:

E – field
probes :
$$E_i = \sqrt{\frac{V_i}{Norm_i \cdot ConvF}}$$

with V_i = compensated signal of channel i (i = x, y, z) $Norm_i$ = sensor sensitivity of channel i (i = x, y, z)

 $\mu V/(V/m)^2$ for E-field Probes

ConvF = sensitivity enhancement in solution

 E_i = electric field strength of channel i in V/m

The RSS value of the field components gives the total field strength (Hermitian magnitude):

$$E_{tot} = \sqrt{E_x^2 + E_y^2 + E_z^2}$$

The primary field data are used to calculate the derived field units.

The measurement/integration time per point, as specified by the system manufacturer is >500ms.

The signal response time is evaluated as the time required by the system to reach 90% of the expected final value after an on/off switch of the power source with an integration time of 500ms and a probe response time of <5 ms. In the current implementation, DASY5 waits longer than 100ms after having reached the grid point before starting a measurement, i.e., the response time uncertainty is negligible.

If the device under test does not emit a CW signal, the integration time applied to measure the electric field at a specific point may introduce additional uncertainties due to the discretization. The tolerances for the different systems had the worst-case of 2.6%.

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TEST PROCEDURE 5.

RF EMISSIONS

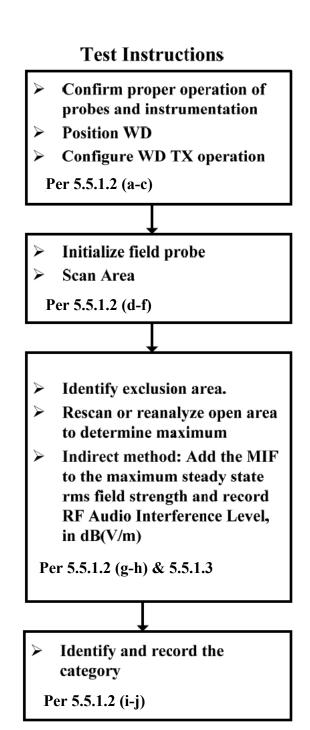


Figure 5-1 RF Emissions Flow Chart

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Test Setup

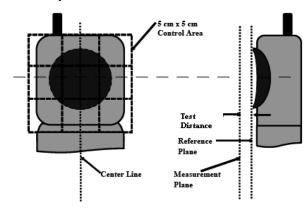


Figure 5-2 E-Field Emissions Test Setup Diagram (See Test Photographs for actual WD scan grid overlay)

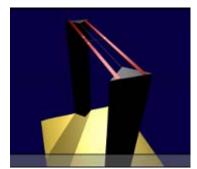


Figure 5-3 **HAC Phantom**

RF Emissions Test Procedure:

The following illustrate a typical RF emissions test scan over a wireless communications device:

- 1. Proper operation of the field probe, probe measurement system, other instrumentation, and the positioning system was confirmed.
- 2. WD is positioned in its intended test position, acoustic output point of the device perpendicular to the field probe.
- 3. The WD operation for maximum rated RF output power was configured and confirmed with the base station simulator, at the test channel and other normal operating parameters as intended for the test. The battery was ensured to be fully charged before each test.
- 4. The center sub-grid was centered over the center of the acoustic output (also audio band magnetic output, if applicable). The WD audio output was positioned tangent (as physically possible) to the measurement plane.
- 5. A surface calibration was performed before each setup change to ensure repeatable spacing and proper maintenance of the measurement plane using the HAC Phantom.
- 6. The measurement system measured the field strength at the reference location.
- 7. Measurements at 2mm or 5mm increments in the 5 x 5 cm region were performed at a distance 15 mm from the center point of the probe measurement element to the WD. A 360° rotation about the azimuth axis at the maximum interpolated position was measured. For the worst-case condition, the peak reading from this rotation was used in re-evaluating the HAC category.
- 8. The system performed a drift evaluation by measuring the field at the reference location. If the power drift deviated by more than 5%, the HAC test and drift measurements were repeated.

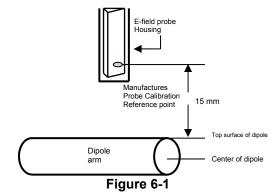
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6. SYSTEM CHECK

System Check Parameters

The input signal was an un-modulated continuous wave. The following points were taken into consideration in performing this check:

- Average Input Power P = 100mW RMS (20dBm RMS) after adjustment for return loss
- The test fixture must meet the 2 wavelength separation criterion
- The proper measurement of the 15 mm probe to dipole separation, which is measured from top surface of the dipole to the calibration reference point of the sensor, defined by the probe manufacturer is shown in the following diagram:



Separation Distance from Dipole to Field Probe

RF power was recorded using both an average reading meter and a peak reading meter. Readings of the probe are provided by the measurement system.

To assure proper operation of the near-field measurement probe the input power to the dipole shall be commensurate with the full rated output power of the wireless device [e.g. - for a cellular phone wireless device the average peak antenna input power will be on the order of 100mW (20dBm) RMS] after adjustment for any mismatch.

II. Validation Procedure

A dipole antenna meeting the requirements given in C63.19 was placed in the position normally occupied by the WD.

The length of the dipole was scanned, and the average peak value was recorded.

Measurement of CW

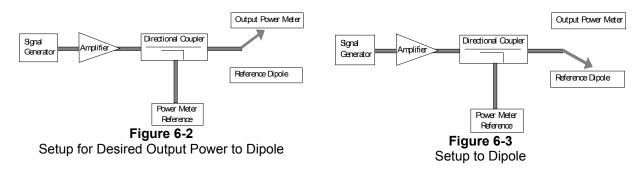
Using the near-field measurement system, scan the antenna over the radiating dipole and record the greatest field reading observed. Due to the nature of E-fields about free-space dipoles, the two E-field peaks measured over the dipole are averaged to compensate for non-parallelity of the setup (see manufacturer method on dipole calibration certificates, page 2). Field strength measurements shall be made only when the probe is stationary.

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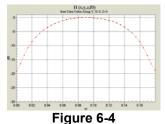
REV 3.2.M

RF power was recorded using both an average and a peak power reading meter.



Using this setup configuration, the signal generator was adjusted for the desired output power (100mW) at a specified frequency. The reference power from the coupled port of the directional coupler is recorded. Next, the output cable is connected to the reference dipole, as shown in Figure 6-3.

The input signal level was adjusted until the reference power from the coupled port of the directional coupler was the same as previously recorded, to compensate for the impedance mismatch between the output cable and the reference dipole. To assure proper operation of the near-field measurement probe the input power to the reference dipole was verified to the full rated output power of the wireless device. The dipole was secured in a holder in a manner to meet the 20 dB reflection. The near-field measurement probe was positioned over the dipole. The antenna was scanned over the appropriate sized area to cover the dipole from end to end. SPEAG uses 2D interpolation algorithms between the measured points. Please see below two dimensional plots showing that the interpolated values interpolate smoothly between 5mm steps for a free-space RF dipole:



2-D Raw Data from scan along dipole axis

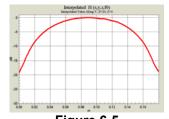
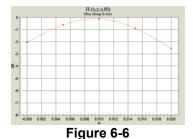


Figure 6-5
2-D Interpolated points from scan along dipole axis



2-D Raw Data from scan along transverse axis



2-D Interpolated points from scan along transverse axis

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REV 3.2.M

III. System Check Results

Validation Results

Date	Frequency (MHz)	Probe S/N	DAE S/N	Dipole S/N	Input Power (dBm)	E-field Result (V/m)	Target Field (V/m)	% Deviation
4/9/2018	835	2335	859	1082	20.0	109.9	106.8	2.9%
4/9/2010	1880	2335	859	1064	20.0	89.7	89.6	0.1%

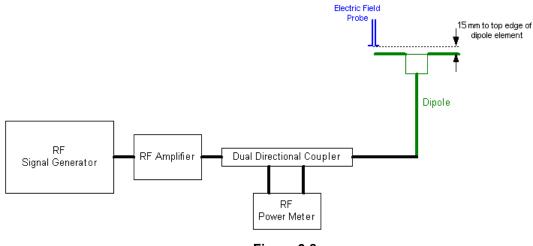


Figure 6-8 System Check Setup

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MODULATION INTERFERENCE FACTOR 7.

I. Measuring Modulation Interference Factors

For any specific fixed and repeatable modulated signal, a modulation interference factor (MIF, expressed in dB) may be determined that relates its interference potential to its steady-state RMS signal level or average power level. This factor is a function only of the audio-frequency amplitude modulation characteristics of the signal and is the same for field-strength and conducted power measurements. The MIF is valid only for a specific repeatable audio-frequency amplitude modulation characteristic; any change in modulation characteristic requires determination and application of a new MIF.

The MIF may be determined using a radiated RF field or a conducted RF signal:

- a. Using RF illumination or conducted coupling, apply the specific modulated signal in question to the measurement system at a level within its confirmed operating dynamic range.
- b. Measure the steady-state RMS level at the output of the fast probe or sensor.
- c. Measure the steady-state average level at the weighting output.
- d. Without changing the square-law detector or weighting system, and using RF illumination or conducted coupling, substitute for the specific modulated signal a 1 kHz, 80% amplitude modulated carrier at the same frequency and adjust its strength until the level at the weighting output equals the step c) measurement.
- e. Without changing the carrier level from step d), remove the 1 kHz modulation and again measure the steady-state RMS level indicated at the output of the fast probe or sensor.
- The MIF for the specific modulation characteristic is provided by the ratio of the step e) measurement to the step b) measurement, expressed in dB (20 × log[(step e)/(step b)]).

The following procedure was used to measure the MIF using the SPEAG Audio Interference Analyzer (AIA), Type No: SE UMS 170 CB, Serial No.: 1010:

- 1. The device was placed into a simulated call using a base station simulator or set to transmit using test software for a given mode.
- 2. The device was then set to continuously transmit at maximum power.
- 3. Using a coupler if needed, the device output signal was connected to the RF In port of the AIA, which was connected to a desktop computer. Alternatively, a radiated RF signal may be used with the AIA's built-in antenna.
- 4. The MIF measurement procedure in the DASY software was run, and the resulting MIF value was recorded.
- Steps 1-4 were repeated for all CMRS air interfaces, frequency bands, and modulations.

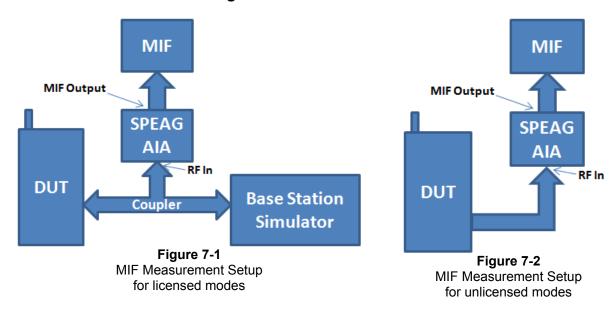
The modulation interference factors obtained were applied to readings taken of the actual wireless device in order to obtain an accurate audio interference level reading using the formula:

Audio Interference Level [dB(V/m)] = 20 * log[Raw Field Value (V/m)] + MIF (dB)

Because the MIF value is output power independent, MIF values for a given mode should be constant across all devices; however, per C63.19-2011 §D.7, MIF values should be measured for each device being evaluated. The voice modes for this device have been investigated in this section of the report.

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II. MIF Measurement Block Diagrams



III. Measured Modulation Interference Factors:

Table 7-1 CDMA Modulation Interference Factors¹

Ma	Mode		Cell			PCS			
Mode		1013	384	777	25	600	1175		
	RC1/SO3	3.09	3.09	3.11	3.05	3.07	3.07		
CDMA	RC1/SO55	-17.76	-17.87	-17.65	-17.12	-17.05	-17.12		
	EvDO	-16.56	-16.79	-16.60	-16.60	-16.34	-16.84		

Table 7-2 GSM Modulation Interference Factors¹

	Com modulation memorial raction								
Mode			GSM850		GSM1900				
IVIC	Jue	128	190	251	512 661 810				
GSM	Voice	3.56	3.56	3.56	3.57	3.56	3.56		
GSIWI	EDGE	4.51	4.50	4.55	4.02	4.02	4.01		

Table 7-3 LIMTS Modulation Interference Factors¹

ONTS Modulation interference Factors								
Mode			UMTS V		UMTS II			
		4132	4183	4233	9262	9400	9538	
	12.2 kbps RMC	-19.96	-20.99	-22.68	-21.05	-21.46	-20.82	
UMTS	12.2 kbps AMR	-20.80	-20.65	-21.41	-22.01	-21.85	-22.08	
	HSUPA Subtest1	-14.53	-14.45	-14.45	-14.42	-14.73	-14.16	

¹ Note: Measured MIF values may be lower than sample MIF values provided in ANSI C63.19-2011 Annex D.7 Table D.5 due to manufacturing variations for each device, however per Annex D.7, the sample MIF values of Table D.5 are not intended to substitute for measurements of actual devices under test and their respective operating modes.

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Table 7-4LTE FDD Modulation Interference Factors^{1,3,4}

			vioadiation i	illenerence i	aotoro		
LTE Band	Frequency [MHz]	Channel	Bandwidth [MHz]	Modulation	RB Size	RB Offset	MIF [dB]
13	782.0	23230	10	16QAM	1	0	-10.18
5	836.5	20525	10	16QAM	1	0	-9.93
4	1732.5	20175	20	16QAM	1	0	-9.51
2	1880.0	18900	20	16QAM	1	0	-9.67
7	2535.0	21100	20	16QAM	1	0	-10.00
4	1732.5	20175	20	QPSK	1	0	-14.02
4	1732.5	20175	20	16QAM	1	50	-9.48
4	1732.5	20175	20	16QAM	1	99	-9.22
4	1732.5	20175	20	16QAM	50	0	-16.41
4	1732.5	20175	20	16QAM	100	0	-17.78
4	1732.5	20175	15	16QAM	1	74	-10.11
4	1732.5	20175	10	16QAM	1	49	-10.25
4	1732.5	20175	5	16QAM	1	24	-9.56
4	1732.5	20175	3	16QAM	16QAM 1		-9.99
4	1732.5	20175	1.4	16QAM	1	5	-9.71

Table 7-5 802.11b (2.4GHz, SISO) Modulation Interference Factors^{1,2}

	802.11b MIF Measurements [dB]								
Mode	Data Rate [Mbps]								
	1	2	5.5	11					
802.11b	-14.43	-14.43 -13.75 -11.16 -10.74							

Table 7-6 802.11g (2.4GHz, SISO) Modulation Interference Factors^{1,2}

	802.11g MIF Measurements [dB]										
Mode	Data Rate [Mbps]										
	6	9	12	18	24	36	48	54			
802.11g	-11.52	-10.84	-10.30	-9.64	-9.40	-9.48	-9.98	-10.24			

¹ Note: Measured MIF values may be lower than sample MIF values provided in ANSI C63.19-2011 Annex D.7 Table D.5 due to manufacturing variations for each device, however per Annex D.7, the sample MIF values of Table D.5 are not intended to substitute for measurements of actual devices under test and their respective operating modes.

⁴ Note: Since LTE Band 4 at 20 MHz bandwidth is the overall worst-case LTE MIF and does not support 3 nonoverlapping channels, MIF measurements were made only on the middle channel

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² Note: WIFI MIF values were found to be independent of the transmit channel.

³ Note: All FDD LTE bands were found to have substantially similar MIF values given similar RB, BW, and modulation configurations.

Table 7-7 802.11n (2.4GHz, SISO) Modulation Interference Factors^{1,2}

	802.11n (2.4GHz) MIF Measurements [dB]											
Mode	Data Rate [Mbps]											
	6.5 13 19.5 26 39 52 58.											
802.11n	-7.94											

Table 7-8

802.11a (5GHz, 20MHz BW, SISO) Modulation Interference Factors^{1,2}

		002.114	802.11a MIF Measurements [dB]										
Mode Data Rate [Mbps]													
		6	9	12	18	24	36	48	54				
	802.11a	-8.00	-7.70	-6.89	-10.90	-5.86	-5.90	-5.64	-11.97				

Table 7-9

802.11n (5GHz, 20MHz BW, SISO) Modulation Interference Factors^{1,2}

		20MHz BW 802.11n (5GHz) MIF Measurements [dB]									
Mode	Data Rate [Mbps]										
	6.5	13	19.5	26	39	52	58.5	65			
802.11n	-8.05	-6.93	-6.33	-5.56	-6.11	-5.30	-6.93	-12.21			

Table 7-10

802.11n (5GHz, 40MHz BW, SISO) Modulation Interference Factors^{1,2}

		40MHz BW 802.11n (5GHz) MIF Measurements [dB]									
Mode	Data Rate [Mbps]										
	13.5	27	40.5	54	81	108	121.5	135			
802.11n	-10.85										

¹ Note: Measured MIF values may be lower than sample MIF values provided in ANSI C63.19-2011 Annex D.7 Table D.5 due to manufacturing variations for each device, however per Annex D.7, the sample MIF values of Table D.5 are not intended to substitute for measurements of actual devices under test and their respective operating modes.

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² Note: WIFI MIF values were found to be independent of the transmit channel.

8. RF CONDUCTED POWER MEASUREMENTS

I. Procedures Used to Establish RF Signal for HAC Testing

The handset was placed into a simulated call using a base station simulator in a shielded chamber. Such test signals offer a consistent means for testing HAC and are recommended for evaluating HAC. Measurements were taken with a fully charged battery. In order to verify that the device was tested and maintained at full power, this was configured with the base station simulator.

II. HAC Measurement Conditions

Output Power Verification

Maximum output power is verified on the High, Middle and Low channels for all applicable air interfaces. See Table 8-1 for air interface specific settings of transmit power parameters.

> Table 8-1 **Power Control Parameters and Settings by Air Interface**

Air Interface:	Parameter Name:	Parameter Set To:
CDMA	Power Control Bits	"All Up"
GSM	PCL	GSM850: "5"; GSM1900: "0"
UMTS	TPC	"All 1's"
LTE	TPC	"Max Power"
WIFI	PLS	Mfr Specified

III. Setup Used to Measure RF Conducted Powers

Power measurements for licensed modes were performed using a base station simulator under digital average power. Power measurements for unlicensed modes were performed using a power meter and power sensor.

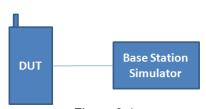


Figure 8-1 Power Measurement Setup for licensed modes

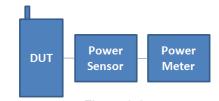


Figure 8-2 Power Measurement Setup for unlicensed modes

IV. CDMA Conducted Powers

Band	Channel	Frequency	SO2 [dBm]	SO2 [dBm]	SO2 [dBm]	SO55 [dBm]	SO55 [dBm]	SO9 [dBm]	SO9 [dBm]	SO3 [dBm]	SO3 [dBm]	SO3 [dBm]	1x EvDO Rev. A [dBm]
	F-RC	MHz	RC1	RC3	RC4	RC1	RC3	RC2	RC5	RC1	RC3	RC4	(RETAP)
	1013	824.7	23.61	23.56	23.62	23.56	23.60	23.60	23.58	23.61	23.62	23.63	23.72
Cellular	384	836.52	23.62	23.60	23.61	23.59	23.62	23.57	23.60	23.60	23.61	23.61	23.59
	777	848.31	23.50	23.47	23.46	23.49	23.47	23.47	23.46	23.47	23.49	23.48	23.58
	25	1851.25	22.76	22.77	22.78	22.77	22.79	22.78	22.77	22.93	22.77	22.76	22.77
PCS	600	1880	22.80	22.82	22.83	22.85	22.86	22.82	22.81	22.88	22.79	22.82	22.84
	1175	1908.75	22.97	22.96	22.94	22.95	22.96	22.94	22.97	23.04	22.95	22.95	22.94

¹ Note: This device utilizes independent power reduction mechanisms for CDMA BC0/1 in held-to-ear scenarios.

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V. GSM Conducted Powers

Table 8-2 **GSM Maximum Conducted Powers**

Gow waxiiilalii Goliaactea Fowers							
Band	Channel	GSM [dBm] CS (1 Slot)	EDGE [dBm] 1 Tx Slot				
	128	31.97	25.97				
GSM 850	190	31.94	25.81				
	251	31.95	25.53				

Table 8-3 **GSM Reduced Conducted Powers**¹

Band	Channel	GSM [dBm] CS (1 Slot)	EDGE [dBm] 1 Tx Slot	
	512	26.62	24.19	
GSM 1900	661	26.65	24.56	
	810	26.77	24.61	

¹ Note: This device utilizes independent power reduction mechanisms for GSM1900 in held-to-ear scenarios.

VI. UMTS Conducted Powers

Table 8-4 **UMTS Maximum Conducted Powers**

Mode	3GPP 34.121 Subtest	Cellular Band [dBm]			
	Oublest	4132	4183	4233	
WCDMA	12.2 kbps RMC	23.03	23.01	22.97	
	12.2 kbps AMR	22.96	22.97	22.99	
HSUPA	Subtest 1	22.31	22.34	22.32	

Table 8-5 **UMTS Reduced Conducted Powers¹**

Mode	3GPP 34.121 Subtest	PCS Band [dBm]			
	Gublest	9262	9400	9538	
WCDMA	12.2 kbps RMC	21.91	21.82	21.90	
	12.2 kbps AMR	21.93	21.97	22.02	
HSUPA	Subtest 1	21.31	21.21	21.19	

¹ Note: This device utilizes independent power reduction mechanisms for UMTS II in held-to-ear scenarios.

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VII. LTE Conducted Powers

a. LTE Band 13

Table 8-6
LTE Band 13 (780.0MHz) Conducted Powers – 10MHz Bandwidth

			LTE Band 13 10 MHz Bandwidth		
			Mid Channel		
Modulation	RB Size	3 Size RB Offset	23230 (782.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			Conducted Power [dBm]	0011 [05]	
	1	0	24.07		0
	1	25	24.08	0	0
	1	49	23.99		0
QPSK	25	0	23.07		1
	25	12	22.92	0-1	1
	25	25	23.00		1
	50	0	23.03		1
	1	0	23.06		1
	1	25	23.05	0-1	1
	1	49	22.95		1
16QAM	25	0	22.01		2
	25	12	21.98	0-2	2
	25	25	21.94	0-2	2
	50	0	22.01		2

Table 8-7
LTE Band 13 (780.0MHz) Conducted Powers – 5MHz Bandwidth

	LTE Band 13									
	5 MHz Bandwidth									
			Mid Channel							
Modulation	RB Size	RB Offset	23230	MPR Allowed per	MPR [dB]					
			(782.0 MHz)	3GPP [dB]						
			Conducted Power							
			[dBm]							
	1	0	23.99		0					
	1	12	23.92	0	0					
	1	24	23.78	1	0					
QPSK	12	0	22.81		1					
	12	6	22.79	0-1	1					
	12	13	22.75	0-1	1					
	25	0	22.78		1					
	1	0	22.65		1					
	1	12	22.56	0-1	1					
	1	24	23.06		1					
16QAM	12	0	21.91		2					
	12	6	21.87	0-2	2					
	12	13	21.81	0-2	2					
	25	0	21.84		2					

Note: Since LTE Band 13 at 5MHz bandwidth does not support 3 non-overlapping channels, conducted power measurements were made only on the middle channel.

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b. LTE Band 5

Table 8-8 LTE Band 5 (836.5MHz) Conducted Powers – 10MHz Bandwidth

	LTE Band 5 (Cell) 10 MHz Bandwidth								
			Mid Channel						
Modulation	RB Size	RB Offset	20525 (836.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]				
			Conducted Power [dBm]						
	1	0	24.02		0				
	1	25	23.97	0	0				
	1	49	23.97		0				
QPSK	25	0	22.95		1				
	25	12	22.88	0-1	1				
	25	25	22.89	0-1	1				
	50	0	22.93		1				
	1	0	23.01		1				
	1	25	22.93	0-1	1				
	1	49	22.92		1				
16QAM	25	0	22.00		2				
	25	12	21.98	0-2	2				
	25	25	21.99	0-2	2				
	50	0	22.02		2				

Note: Since LTE Band 5 at 10MHz bandwidth does not support 3 non-overlapping channels, conducted power measurements were made only on the middle channel.

LTE Band 5 (836.5MHz) Conducted Powers - 5MHz Bandwidth

	LTE Band 5 (636.5MHz) Conducted Powers – 5MHz Bandwidth									
	LTE Band 5 (Cell)									
			T.	5 MHz Bandwidth						
			Low Channel	Mid Channel	High Channel					
Modulation	RB Size	RB Offset	20425 (826.5 MHz)	20525 (836.5 MHz)	20625 (846.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]			
				Conducted Power [dBm	1]					
	1	0	24.27	23.94	24.35		0			
	1	12	24.17	23.91	24.32	0	0			
	1	24	24.21	23.91	24.31		0			
QPSK	12	0	23.05	22.98	23.22		1			
	12	6	23.02	23.01	23.20	0-1	1			
	12	13	23.04	22.96	23.19	0-1	1			
	25	0	23.00	22.97	23.18		1			
	1	0	23.09	22.91	23.18		1			
	1	12	22.93	22.85	23.13	0-1	1			
	1	24	22.93	22.86	23.19		1			
16QAM	12	0	21.98	21.94	22.09		2			
	12	6	21.97	21.88	22.05	0-2	2			
	12	13	22.00	21.86	21.95	0-2	2			
	25	0	22.01	21.97	22.15		2			

Table 8-10 LTE Band 5 (836.5MHz) Conducted Powers – 3MHz Bandwidth

		Bana 0	(000.0.0		011010 011	TIZ Ballawiat	•
				LTE Band 5 (Cell)			
				3 MHz Bandwidth			
			Low Channel	Mid Channel	High Channel		
Modulation	RB Size	RB Offset	20415 (825.5 MHz)	20525 (836.5 MHz)	20635 (847.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			(Conducted Power [dBm]		
	1	0	24.12	24.07	24.44		0
	1	7	24.09	24.04	24.42	0	0
	1	14	24.10	24.04	24.39	1	0
QPSK	8	0	23.02	22.96	23.24		1
	8	4	23.03	22.95	23.22	0.4	1
	8	7	23.02	22.90	23.19	0-1	1
	15	0	23.06	22.99	23.25		1
	1	0	23.19	23.04	23.19		1
	1	7	23.04	22.89	23.15	0-1	1
	1	14	22.96	22.80	23.13		1
16QAM	8	0	21.98	22.01	22.12		2
	8	4	21.94	22.03	22.14	0-2	2
	8	7	21.93	22.05	22.09	0-2	2
	15	0	22.00	21.92	22.10		2

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Table 8-11 LTE Band 5 (836.5MHz) Conducted Powers – 1.4MHz Bandwidth

	LIL Balla 3 (030.3MITZ) Collacted Fowers - 1.4MITZ Ballawiatii										
				LTE Band 5 (Cell)							
	1	1		1.4 MHz Bandwidth		1					
			Low Channel	Mid Channel	High Channel						
Modulation	RB Size	RB Offset	20407 (824.7 MHz)	20525 (836.5 MHz)	20643 (848.3 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]				
			(Conducted Power [dBm	1]						
	1	0	24.18	24.17	24.45		0				
	1	2	24.15	24.18	24.40		0				
	1	5	24.19	24.17	24.43	0	0				
QPSK	3	0	24.16	24.01	24.29		0				
	3	2	24.18	24.02	24.31		0				
	3	3	24.19	24.06	24.30		0				
	6	0	23.10	22.94	23.30	0-1	1				
	1	0	22.89	22.65	23.04		1				
	1	2	23.00	22.56	23.02		1				
	1	5	23.07	22.55	23.13	0-1	1				
16QAM	3	0	23.14	22.80	23.24	0-1	1				
	3	2	23.16	22.78	23.22	1	1				
	3	3	23.18	22.82	23.20		1				
	6	0	22.08	22.03	22.14	0-2	2				

c. LTE Band 4

Table 8-12
LTE Band 4 (1732.5MHz) Reduced Conducted Powers – 20MHz Bandwidth¹

			LTE Band 4 (AWS) 20 MHz Bandwidth		
			Mid Channel		
Modulation	RB Size	RB Offset	20175 (1732.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			Conducted Power [dBm]	0011 [ub]	
	1	0	22.43		0
	1	50	22.41	0	0
	1	99	22.42		0
QPSK	50	0	21.38		1
	50	25	21.37	0-1	1
	50	50	21.33	0-1	1
	100	0	21.35		1
	1	0	21.36		1
	1	50	21.41	0-1	1
	1	99	21.40		1
16QAM	50	0	20.34		2
	50	25	20.43	0-2	2
	50	50	20.41	0-2	2
	100	0	20.31		2

Note: Since LTE Band 4 at 20MHz bandwidth does not support 3 non-overlapping channels, conducted power measurements were made only on the middle channel.

Table 8-13
LTE Band 4 (1732.5MHz) Reduced Conducted Powers – 15MHz Bandwidth¹

	Julia T	1702.01	miz, nead		ica i owcis	- I JIVII IZ DE	awiatii	
				LTE Band 4 (AWS) 15 MHz Bandwidth				
			Lov	Low Channel	Mid Channel	High Channel		
Modulation	RB Size	RB Offset	20025 (1717.5 MHz)	20175 (1732.5 MHz)	20325 (1747.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]	
			(Conducted Power [dBm	1]			
	1	0	22.80	22.72	22.78		0	
	1	36	22.76	22.73	22.77	0	0	
	1	74	22.77	22.69	22.76		0	
QPSK	36	0	21.72	21.67	21.73	0-1	1	
	36	18	21.75	21.66	21.72		1	
	36	37	21.72	21.68	21.68		1	
	75	0	21.73	21.66	21.69		1	
	1	0	21.53	21.72	21.79		1	
	1	36	21.48	21.65	21.73	0-1	1	
	1	74	21.81	21.61	21.65		1	
16QAM	36	0	20.76	20.71	20.68		2	
ľ	36	18	20.78	20.67	20.70	0-2	2	
	36	37	20.77	20.68	20.69	0-2	2	
	75	0	20.74	20.68	20.71		2	

¹ Note: This device utilizes independent power reduction mechanisms for LTE Band 4 in held-to-ear scenarios.

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Table 8-14
LTE Band 4 (1732.5MHz) Reduced Conducted Powers – 10MHz Bandwidth¹

	. Dana -	(1702.0	mile) iteau	Jeu Conduct	ca i owcis	TOWN 12 Buil	awiatii
				LTE Band 4 (AWS) 10 MHz Bandwidth			
						1	
			Low Channel	Mid Channel	High Channel		
Modulation	RB Size	RB Offset	20000 (1715.0 MHz)	20175 (1732.5 MHz)	20350 (1750.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			(Conducted Power [dBm	1]		
	1	0	22.77	22.71	22.68		0
	1	25	22.78	22.73	22.72	0-1	0
İ	1	49	22.82	22.72	22.69		0
QPSK	25	0	21.65	21.66	21.70		1
	25	12	21.69	21.63	21.69		1
	25	25	21.68	21.64	21.68		1
	50	0	21.67	21.65	21.71		1
	1	0	21.72	21.66	21.64		1
	1	25	21.44	21.65	21.63	0-1	1
	1	49	21.58	21.67	21.77		1
16QAM	25	0	20.70	20.58	20.74		2
	25	12	20.73	20.60	20.75	1	2
	25	25	20.75	20.57	20.72	0-2	2
	50	0	20.74	20.73	20.76	1	2

Table 8-15 LTE Band 4 (1732.5MHz) Reduced Conducted Powers – 5MHz Bandwidth¹

				LTE Band 4 (AWS) 5 MHz Bandwidth			
			Low Channel	Mid Channel	High Channel		
Modulation	RB Size	RB Offset	19975 20175 20375 (1712.5 MHz) (1732.5 MHz) (1752.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]		
				Conducted Power [dBn	1]		
	1	0	22.75	22.63	22.83		0
	1	12	22.76	22.64	22.85	0	0
Ī	1	24	22.79	22.65	22.83		0
QPSK	12	0	21.71	21.65	21.70		1
	12	6	21.72	21.64	21.71	0-1	1
	12	13	21.69	21.66	21.72		1
	25	0	21.71	21.67	21.69		1
	1	0	21.68	21.46	21.55		1
	1	12	21.68	21.52	21.56	0-1	1
	1	24	21.63	21.43	21.59		1
16QAM	12	0	20.60	20.63	20.74		2
	12	6	20.63	20.56	20.76		2
	12	13	20.62	20.61	20.75	0-2	2
Ī	25	0	20.69	20.66	20.73	1	2

Table 8-16

LTE Band 4 (1732.5MHz) Reduced Conducted Powers – 3MHz Bandwidth¹

				LTE Band 4 (AWS) 3 MHz Bandwidth			
			Low Channel	Mid Channel	High Channel		
Modulation	RB Size	RB Offset	19965 (1711.5 MHz)	20175 (1732.5 MHz)	20385 (1753.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
				Conducted Power [dBm	1]		
	1	0	22.85	22.76	22.65		0
	1	7	22.88	22.80	22.68	0	0
Ī	1	14	22.87	22.76	22.65		0
QPSK	8	0	21.74	21.65	21.64		1
	8	4	21.75	21.67	21.62	0-1	1
	8	7	21.78	21.67	21.63	0-1	1
	15	0	21.77	21.66	21.63		1
	1	0	21.69	21.58	21.83		1
	1	7	21.73	21.60	21.82	0-1	1
	1	14	21.74	21.62	21.80		1
16QAM	8	0	20.75	20.78	20.70		2
	8	4	20.72	20.77	20.73	0-2	2
	8	7	20.76	20.75	20.72	0-2	2
	15	0	20.84	20.72	20.68		2

¹ Note: This device utilizes independent power reduction mechanisms for LTE Band 4 in held-to-ear scenarios.

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Table 8-17 LTE Band 4 (1732.5MHz) Reduced Conducted Powers - 1.4MHz Bandwidth¹

		1	<u>, , , , , , , , , , , , , , , , , </u>				
				LTE Band 4 (AWS)			
				1.4 MHz Bandwidth			
			Low Channel Mid Channel High Channel		High Channel		
Modulation	RB Size	RB Offset	19957 (1710.7 MHz)	20175 (1732.5 MHz)	20393 (1754.3 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			(Conducted Power [dBm]		
	1	0	22.92	22.85	22.67		0
	1	2	22.87	22.87	22.66	0	0
	1	5	22.91	22.86	22.67		0
QPSK	3	0	22.87	22.74	22.73		0
	3	2	22.93	22.75	22.70		0
	3	3	22.94	22.77	22.68		0
	6	0	21.86	21.69	21.62	0-1	1
	1	0	21.74	21.40	21.52		1
	1	2	21.66	21.42	21.53		1
	1	5	21.72	21.45	21.57	0-1	1
16QAM	3	0	21.77	21.59	21.46	0-1	1
	3	2	21.74	21.60	21.45		1
	3	3	21.76	21.61	21.48		1
Ì	6	0	20.79	20.62	20.69	0-2	2

d. LTE Band 2

Table 8-18 LTE Band 2 (1880.0MHz) Reduced Conducted Powers – 20MHz Bandwidth¹

			•	LTE Band 2 (PCS) 20 MHz Bandwidth			
			Low Channel	Low Channel Mid Channel High Channel			
Modulation	RB Size	RB Offset	18700 (1860.0 MHz)	18900 (1880.0 MHz)	19100 (1900.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			(Conducted Power [dBm	1]		
	1	0	22.46	22.67	22.56		0
	1	50	22.42	22.67	22.61	0	0
	1	99	22.50	22.70	22.71		0
QPSK	50	0	21.51	21.62	21.59	0-1	1
	50	25	21.53	21.63	21.69		1
	50	50	21.48	21.65	21.63		1
	100	0	21.43	21.61	21.60		1
	1	0	21.70	21.65	21.66		1
	1	50	21.69	21.73	21.60	0-1	1
	1	99	21.61	21.78	21.73		1
16QAM	50	0	20.43	20.65	20.63		2
	50	25	20.47	20.65	20.61	1 ,,	2
	50	50	20.49	20.67	20.67	0-2	2
	100	0	20.54	20.69	20.61	1	2

Table 8-19 LTE Band 2 (1880.0MHz) Reduced Conducted Powers – 15MHz Bandwidth¹

		(100010		LTE Band 2 (PCS)		- IJWIIIZ Dali	
				15 MHz Bandwidth			
			Low Channel	Mid Channel	High Channel		
Modulation	RB Size	RB Size RB Offset	18675 (1857.5 MHz)	18900 (1880.0 MHz)	19125 (1902.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
				Conducted Power [dBm	1]		
	1	0	22.61	22.71	22.77		0
	1	36	22.66	22.70	22.75	0	0
	1	74	22.65	22.66	22.76		0
QPSK	36	0	21.56	21.74	21.71	- 0-1	1
	36	18	21.57	21.72	21.69		1
	36	37	21.61	21.70	21.70		1
	75	0	21.57	21.71	21.68	1	1
	1	0	21.26	21.78	21.62		1
	1	36	21.27	21.68	21.61	0-1	1
	1	74	21.36	21.64	21.59	1	1
16QAM	36	0	20.77	20.74	20.64		2
	36	18	20.61	20.73	20.64	1 ,,	2
	36	37	20.62	20.71	20.65	0-2	2
	75	0	20.56	20.71	20.63	1 1	2

¹ Note: This device utilizes independent power reduction mechanisms for LTE Band 2/4 in held-to-ear scenarios.

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Table 8-20 LTE Band 2 (1880.0MHz) Reduced Conducted Powers - 10MHz Bandwidth¹

	. Dana .	. (. 0 0 0 . 0	mile, itoaac	ca conaact	04 1 011010	TOWN 12 Dan	attiatii
				LTE Band 2 (PCS)			
				10 MHz Bandwidth			
			Low Channel	Mid Channel	High Channel		
Modulation	RB Size	RB Offset	18650 (1855.0 MHz)	18900 (1880.0 MHz)	19150 (1905.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
				Conducted Power [dBm	n]		
	1	0	22.69	22.68	22.74		0
	1	25	22.63	22.64	22.71	0	0
	1	49	22.68	22.63	22.75		0
QPSK	25	0	21.57	21.59	21.51	0-1	1
	25	12	21.53	21.58	21.55		1
	25	25	21.56	21.58	21.57		1
	50	0	21.54	21.60	21.56		1
	1	0	21.51	21.42	21.36		1
	1	25	21.55	21.48	21.37	0-1	1
	1	49	21.53	21.57	21.35		1
16QAM	25	0	20.58	20.57	20.60		2
	25	12	20.59	20.55	20.58	0-2	2
	25	25	20.62	20.59	20.61	1 0-2	2
	50	0	20.57	20.62	20.52		2

Table 8-21 LTF Band 2 (1880 0MHz) Reduced Conducted Powers - 5MHz Bandwidth¹

			•	LTE Band 2 (PCS) 5 MHz Bandwidth			
					High Channel		
Modulation	RB Size	RB Offset	18625 (1852.5 MHz)	18900 (1880.0 MHz)	19175 (1907.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
				Conducted Power [dBm	n]		
	1	0	22.61	22.68	22.77		0
	1	12	22.60	22.70	22.79	0	0
	1	24	22.65	22.67	22.80		0
QPSK	12	0	21.50	21.67	21.61		1
	12	6	21.51	21.69	21.60	0-1	1
	12	13	21.53	21.68	21.64	0-1	1
	25	0	21.54	21.70	21.59		1
	1	0	21.68	21.66	21.58		1
	1	12	21.73	21.61	21.64	0-1	1
	1	24	21.74	21.60	21.63		1
16QAM	12	0	20.51	20.66	20.66		2
	12	6	20.48	20.65	20.59	0-2	2
	12	13	20.47	20.68	20.54		2
	25	0	20.48	20.71	20.60	1	2

Table 8-22 LTE Band 2 (1880.0MHz) Reduced Conducted Powers - 3MHz Bandwidth¹

		<u> </u>	///// IE/ / 1 to a a	ood Gondao		OMITIC Barra	******
				LTE Band 2 (PCS)			
				3 MHz Bandwidth			
			Low Channel Mid Channel High Channel		High Channel		
Modulation	RB Size	RB Offset	18615 (1851.5 MHz)	18900 (1880.0 MHz)	19185 (1908.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
				Conducted Power [dBm	1]		
	1	0	22.58	22.75	22.60		0
	1	7	22.60	22.72	22.63	0	0
	1	14	22.63	22.70	22.61		0
QPSK	8	0	21.49	21.64	21.59	0-1	1
•	8	4	21.49	21.61	21.57		1
•	8	7	21.50	21.59	21.59		1
	15	0	21.51	21.65	21.60		1
	1	0	21.56	21.57	21.72		1
ľ	1	7	21.51	21.49	21.73	0-1	1
	1	14	21.53	21.50	21.74		1
16QAM	8	0	20.43	20.62	20.51		2
•	8	4	20.42	20.62	20.52	0-2	2
ľ	8	7	20.45	20.58	20.52		2
ľ	15	0	20.48	20.60	20.60		2

¹ Note: This device utilizes independent power reduction mechanisms for LTE Band 2 in held-to-ear scenarios.

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Table 8-23
LTE Band 2 (1880.0MHz) Reduced Conducted Powers – 1.4MHz Bandwidth¹

		1 1000.0	iiii iz, itoaao	ca conaact	54 1 0 11 0 1 0	1. TIVII IZ DUII	attiatii
				LTE Band 2 (PCS)			
		1		1.4 MHz Bandwidth			
			Low Channel Mid Channel High Channel		High Channel		
Modulation	RB Size	RB Offset	18607 (1850.7 MHz)	18900 (1880.0 MHz)	19193 (1909.3 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			(Conducted Power [dBm	1]		
	1	0	22.66	22.80	22.72		0
	1	2	22.59	22.82	22.70	0	0
QPSK	1	5	22.64	22.86	22.71		0
	3	0	22.60	22.67	22.75		0
	3	2	22.67	22.71	22.74		0
	3	3	22.69	22.70	22.73		0
	6	0	21.56	21.64	21.68	0-1	1
	1	0	21.28	21.53	21.53		1
	1	2	21.24	21.26	21.53		1
	1	5	21.43	21.24	21.54	0-1	1
16QAM	3	0	21.45	21.65	21.60	0-1	1
	3	2	21.38	21.59	21.61		1
	3	3	21.44	21.62	21.63		1
	6	0	20.59	20.58	20.71	0-2	2

¹ Note: This device utilizes independent power reduction mechanisms for LTE Band 2 in held-to-ear scenarios.

e. LTE Band 7

Table 8-24
LTE Band 7 (2535.0MHz) Conducted Powers – 20MHz Bandwidth

		wii. (.			0110.0 20.	VII IZ Ballawic				
				LTE Band 7						
20 MHz Bandwidth										
			Low Channel	Mid Channel	High Channel					
Modulation	RB Size	RB Offset	20850	21100	21350	MPR Allowed per	MPR [dB]			
Modulation	ND SIZE	IND Offset	(2510.0 MHz)	(2535.0 MHz)	(2560.0 MHz)	3GPP [dB]	MIFIX [UD]			
			C	Conducted Power [dBm	1					
	1	0	23.92	24.16	23.89		0			
	1	50	23.96	24.10	23.91	0 0-1	0			
	1	99	24.06	24.10	23.98		0			
QPSK	50	0	22.97	23.00	22.92		1			
	50	25	22.95	22.98	22.94		1			
	50	50	22.98	22.97	22.97		1			
	100	0	22.95	22.99	22.93		1			
	1	0	23.12	23.12	22.82		1			
	1	50	23.07	23.11	22.87	0-1	1			
	1	99	23.08	23.05	22.95		1			
16QAM	50	0	21.90	21.97	21.88		2			
	50	25	21.86	21.97	21.89	0-2	2			
	50	50	21.90	21.93	21.92	0-2	2			
	100	0	21.93	22.01	21.94		2			

Table 8-25 LTE Band 7 (2535.0MHz) Conducted Powers – 15MHz Bandwidth

				LTE Band 7			
				15 MHz Bandwidth			
Modulation	DD 0:	DD 055-14	Low Channel 20825	Mid Channel 21100	High Channel 21375	MPR Allowed per	MDD MD1
	RB Size	RB Offset	(2507.5 MHz)	(2535.0 MHz)	(2562.5 MHz)	3GPP [dB]	MPR [dB]
			(Conducted Power [dBm]		
	1	0	24.13	24.18	24.19		0
	1	36	24.17	24.20	24.25	0	0
	1	74	24.19	24.19	24.31		0
QPSK	36	0	22.89	22.98	22.99		1
	36	18	22.91	22.99	23.01	0-1	1
	36	37	22.92	23.00	23.05	0-1	1
	75	0	22.95	23.02	23.01		1
	1	0	22.90	22.95	22.92		1
	1	36	23.08	22.97	22.96	0-1	1
	1	74	23.11	22.98	23.10		1
16QAM	36	0	21.90	21.98	21.93		2
	36	18	21.88	21.99	21.98	0-2	2
	36	37	21.93	21.97	22.00	0-2	2
	75	0	21.90	21.98	21.98		2

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Table 8-26
LTE Band 7 (2535.0MHz) Conducted Powers – 10MHz Bandwidth

		Julia / (2	-000.01411 12 <i>)</i>	Conducted r	OWCIS 101	WITTE Bullawie	1611			
				LTE Band 7						
10 MHz Bandwidth										
			Low Channel	Mid Channel	High Channel	MPR Allowed per				
Modulation	RB Size	RB Offset	20800	21100	21400		MPR [dB]			
Woddiadon	KD 312e	KD Oliset	(2505.0 MHz)	(2535.0 MHz)	(2565.0 MHz)	3GPP [dB]	MFR [GD]			
			(Conducted Power [dBn	1]					
	1	0	24.07	24.19	24.02		0			
	1	25	24.13	24.23	24.12	0	0			
	1	49	24.15	24.23	24.15		0			
QPSK	25	0	22.86	22.98	22.87	0-1	1			
	25	12	22.85	22.97	22.91		1			
	25	25	22.87	22.99	22.94		1			
	50	0	22.84	22.97	22.89		1			
	1	0	22.89	22.95	22.74		1			
	1	25	22.77	23.02	22.87	0-1	1			
	1	49	22.94	23.06	22.92		1			
16QAM	25	0	21.85	21.92	21.86		2			
	25	12	21.88	21.93	21.88	0-2	2			
	25	25	21.90	21.97	21.90	0-2	2			
	50	0	21.83	21.98	21.89	1	2			

Table 8-27
LTE Band 7 (2535.0MHz) Conducted Powers – 5MHz Bandwidth

		Dana 1	2000.0WII 12)		011013 011	ii iz Balluwiu	(11					
				LTE Band 7								
	5 MHz Bandwidth											
			Low Channel Mid Channel High Channel									
Modulation	RB Size	RB Offset	20775	21100	21425	MPR Allowed per	MPR [dB]					
Modulation	IND GIZE	IND Office	(2502.5 MHz)	(2535.0 MHz)	(2567.5 MHz)	3GPP [dB]	ini it [ub]					
			(Conducted Power [dBm	1]							
	1	0	23.92	24.13	24.18		0					
	1	12	23.96	24.11	24.23	0	0					
	1	24	23.98	24.12	24.26		0					
QPSK	12	0	22.72	22.95	22.86		1					
	12	6	22.75	22.98	22.87	0-1	1					
	12	13	22.77	22.97	22.89	U-1	1					
	25	0	22.73	22.96	22.89		1					
	1	0	22.86	22.95	22.87		1					
	1	12	23.06	22.97	22.84	0-1	1					
	1 24 23.03	23.03	22.84	22.77		1						
16QAM	12	0	21.58	21.98	21.84		2					
	12	6	21.67	21.99	21.87	0-2	2					
	12	13	21.68	21.99	21.89	0-2	2					
	25	0	21.69	21.98	21.85		2					

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VIII. WIFI Conducted Powers (SISO)

Table 8-28 IEEE 802.11b/g/n (2.4GHz, SISO) Reduced Average RF Power¹

2.4GHz Conducted Power [dBm]											
Freg [MHz]	Channel	IEEE Transmission Mode									
ried [winz]	Citatille	802.11b	802.11g	802.11n							
2412	1	15.35	15.35	15.11							
2437	6	15.45	15.64	15.41							
2462	11	15.39	10.73	10.44							

Table 8-29 IEEE 802.11a/n (5GHz, 20MHz BW, SISO) Reduced Average RF Power¹

5GHz (20MHz) Conducted Power [dBm]									
Freq [MHz]	Channel	IEEE Transm	ission Mode						
rieq [wiriz]	Citatillei	802.11a	802.11n						
5180	36	10.20	10.19						
5200	40	10.17	10.01						
5220	44	10.21	10.03						
5240	48	10.08	9.95						
5260	52	10.06	9.94						
5280	56	10.13	10.12						
5300	60	9.85	9.84						
5320	64	9.87	9.85						
5500	100	9.98	9.91						
5600	120	10.02	9.98						
5620	124	10.01	10.05						
5720	144	10.22	10.04						
5745	149	10.31	10.21						
5785	157	10.49	10.35						
5825	165	10.40	10.51						

Table 8-30 IEEE 802.11n (5GHz, 40MHz BW, SISO) Reduced Average RF Power¹

5GHz (40MHz) Conducted Power [dBm]									
Freq [MHz] Channel Mode									
		802.11n							
5190	38	8.86							
5230	46	10.12							
5270	54	10.99							
5310	62	8.37							
5510	102	10.85							
5590	118	10.81							
5630	126	10.86							
5710	142	10.42							
5755	151	10.72							
5795	159	10.82							

¹ Note: This device utilizes independent power reduction mechanisms for the WIFI transmitter in all WIFI modes for held-to-ear scenarios.

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9. JUSTIFICATION OF HELD TO EAR MODES TESTED

I. Analysis of RF Air Interface Technologies

An analysis was performed, following the guidance of §4.3 and §4.4 of the ANSI standard, of the RF air interface technologies being evaluated. The factors that will affect the RF interference potential were evaluated, and the worst-case operating modes were identified and used in the evaluation. A WD's interference potential is a function both of the WD's average near-field field strength and of the signal's audio-frequency amplitude modulation characteristics. Per §4.4, RF air interface technologies that have low power have been found to produce sufficiently low RF interference potential, so it is possible to exempt them from the product testing specified in Clause 5 of the ANSI standard. An RF air interface technology of a device is exempt from testing when its average antenna input power plus its MIF is ≤17dBm for all of its operating modes. RF air interface technologies exempted from testing in this manner are automatically assigned an M4 rating to be used in determining the overall rating for the WD.

The worst-case MIF plus the worst-case average antenna input power for all modes are investigated below to determine the testing requirements for this device.

II. Individual Mode Evaluations

Table 9-1

Max Power + MIF calculations for Low Power Exemptions

IVIAX FOWEL 1 IVIII Calculation	Olio Ioi Low I	OWCI EXCI	приопо	
Air Interface	Maximum Average Power (dBm)	Worst Case MIF (dB)	Total (Power + MIF, dB)	C63.19 Testing Required
CDMA - Full Frame Rate	23.62	-17.05	6.57	No
CDMA - 1/8 th Frame Rate	14.58*	3.11	17.69	Yes
CDMA - EvDO	23.72	-16.34	7.38	No
GSM850	22.94*	3.56	26.50	Yes
GSM1900	17.74*	3.57	21.31	Yes
EDGE850	16.94*	4.55	21.49	Yes**
EDGE1900	15.58*	4.02	19.60	Yes**
UMTS - RMC	23.03	-19.96	3.07	No
UMTS - AMR	22.99	-20.65	2.34	No
HSPA	22.34	-14.16	8.18	No
LTE - FDD	24.45	-9.22	15.23	No
2.4GHz WIFI	15.64	-7.94	7.70	No
5GHz WIFI	10.99	-5.30	5.69	No

^{*} Note: ANSI C63.19-2011 Sec. 4.4 Footnote 20 indicates the use of a long averaging time for measuring the antenna input power when using this method of exclusion. Therefore, the frame averaged power was calculated for these modes in this investigation.

III. Low-Power Exemption Conclusions

Per ANSI C63.19-2011, RF Emissions testing for this device is required only for GSM and CDMA 1/8th Frame Rate voice modes. All other air interfaces are exempt.

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^{**} Note: EDGE data modes were considered but not tested as GSM voice modes were found to be the worst-case modes for the GSM air interface.

OVERALL MEASUREMENT SUMMARY 10.

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I. E-FIELD EMISSIONS:

Table 10-1 HAC Data Summary for CDMA E-field

	TIAO Data Callinary for ODMA E-field											
Mode	Channel	RC/SO	Scan Center	Conducted Power at BS (dBm)	Time Avg. Field (V/m)	Time Avg. Field [dB(V/m)]	MIF (dB)	Audio Interference Level [dB(V/m)]	FCC Limit (dBV/m)	FCC Margin (dB)	Result	Excl Blocks per 5.5
E-Field Emissi	ions											
	1013	RC1/SO3	Acoustic	23.61	22.38	27.00	3.09	30.09	45.00	-14.91	M4	none
Cellular CDMA	384	RC1/SO3	Acoustic	23.60	24.64	27.83	3.09	30.92	45.00	-14.08	M4	none
	777	RC1/SO3	Acoustic	23.47	22.12	26.90	3.11	30.01	45.00	-14.99	M4	none
	25	RC1/SO3	Acoustic	22.93	16.47	24.33	3.05	27.38	35.00	-7.62	M4	none
PCS CDMA	600	RC1/SO3	Acoustic	22.88	15.34	23.72	3.07	26.79	35.00	-8.21	M4	none
	1175	RC1/SO3	Acoustic	23.04	15.32	23.71	3.07	26.78	35.00	-8.22	M4	none

Table 10-2 HAC Data Summary for GSM E-field

Mode	Channel	Scan Center	Conducted Power at BS (dBm)	Time Avg. Field (V/m)	Time Avg. Field [dB(V/m)]	MIF (dB)	Audio Interference Level [dB(V/m)]	FCC Limit (dBV/m)	FCC Margin (dB)	Result	Excl Blocks per 5.5
E-Field Emissi	ions										
	128	Acoustic	31.97	48.15	33.65	3.56	37.21	45.00	-7.79	M4	none
GSM850	190	Acoustic	31.94	55.05	34.82	3.56	38.38	45.00	-6.62	M4	none
	251	Acoustic	31.95	51.40	34.22	3.56	37.78	45.00	-7.22	M4	none
	512	Acoustic	26.62	21.85	26.79	3.57	30.36	35.00	-4.64	M3	none
GSM1900	661	Acoustic	26.65	22.35	26.99	3.56	30.55	35.00	-4.45	M3	none
G3W11900	810	Acoustic	26.77	25.19	28.02	3.56	31.58	35.00	-3.42	M3	none
	810	T-Coil	26.77	25.19	28.02	3.56	31.58	35.00	-3.42	М3	none

II. Worst-case Configuration Evaluation

Table 10-3 Peak Reading 360° Prohe Rotation at Azimuth axis

	Feak Reading 300 Frobe Rotation at Azimuth axis									
Mode	Channel	Scan Center	Time Avg. Field (V/m)	Time Avg. Field [dB(V/m)]	MIF (dB)	Audio Interference Level [dB(V/m)]	FCC Limit (dBV/m)	FCC Margin (dB)	Result	Excl Blocks per 5.5
Probe Rotatio	Probe Rotation at Worst-Case									
GSM1900	810	Acoustic	25.03	27.97	3.56	31.53	35.00	-3.47	М3	none

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Figure 10-1
Sample E-field Scan Overlay
(See Test Setup Photographs for actual WD overlay)

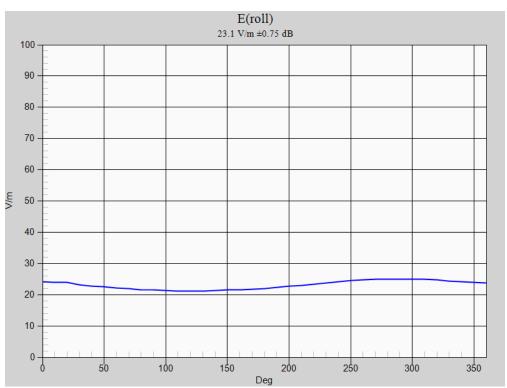


Figure 10-2
Worst-Case Probe Rotation about Azimuth axis

* Note: Locations of probe rotation (with and without exclusions) are shown in Figure 10-1 denoted by the green square markers.

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11. **EQUIPMENT LIST**

Table 11-1 Equipment List

Manufacturer	Model	Description	Cal Date	Cal Interval	Cal Due	Serial Number
Agilent	E4438C	ESG Vector Signal Generator	3/24/2017	Biennial	3/24/2019	MY42082385
Agilent	N5182A	MXG Vector Signal Generator	1/24/2018	Annual	1/24/2019	MY47420651
Amplifier Research	15S1G6	Amplifier	N/A	CBT*	N/A	433978
Anritsu	ML2496A	Power Meter	4/20/2017	Annual	4/20/2018	1306009
Anritsu	MA2411B	Pulse Power Sensor	10/22/2017	Annual	10/22/2018	846215
Anritsu	MA2411B	Pulse Power Sensor	11/28/2017	Annual	11/28/2018	1027293
Anritsu	MA24106A	USB Power Sensor	6/7/2017	Annual	6/7/2018	1244512
Anritsu	MA24106A	USB Power Sensor	6/7/2017	Annual	6/7/2018	1248508
Mini-Circuits	NLP-1200+	Low Pass Filter DC to 1000 MHz	N/A	CBT*	N/A	N/A
Mini-Circuits	NLP-2950+	Low Pass Filter DC to 2700 MHz	N/A	CBT*	N/A	N/A
Mini-Circuits	BW-N20W5	Power Attenuator	N/A	CBT*	N/A	1226
Pasternack	PE2237-20	Bidirectional Coupler	N/A	CBT*	N/A	N/A
Rohde & Schwarz	CMW500	Wideband Radio Communication Tester	7/14/2017	Annual	7/14/2018	140144
Seekonk	NC-100	Torque Wrench (8" lb)	9/1/2016	Biennial	9/1/2018	21053
SPEAG	AIA	Audio Interference Analzyer	N/A	CBT*	N/A	1010
SPEAG	DAE4	Dasy Data Acquisition Electronics	5/17/2017	Annual	5/17/2018	859
SPEAG	CD1880V3	Freespace 1880 MHz Dipole	5/12/2016	Biennial	5/12/2018	1064
SPEAG	CD835V3	Freespace 835 MHz Dipole	5/10/2016	Biennial	5/10/2018	1082
SPEAG	ER3DV6	/6 Freespace E-field Probe		Annual	8/11/2018	2335

Calibration traceable to the National Institute of Standards and Technology (NIST).

*Note: CBT (Calibrated Before Testing). Prior to testing, the measurement paths containing a cable, attenuator, coupler or filter were connected to a calibrated source (i.e. a signal generator) to determine the losses of the measurement path. The power meter offset was then adjusted to compensate for the measurement system losses. This level offset is stored within the power meter before measurements are made. This calibration verification procedure applies to the system verification and output power measurements. The calibrated reading is then taken directly from the power meter after compensation of the losses for all final power measurements.

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12. **MEASUREMENT UNCERTAINTY**

Table 12-1 Uncertainty Estimation Table

Wireless Communications Device Near-Field Measurement							
Uncertainty Estimation							
Uncertainty Component	Data (dB)	Data Type	Prob. Dist.	Divisor	Ci (E)	Unc. (dB)	Notes/Comments
Measurement System		-				•	
RF System Reflections	0.50	Tolerance	N	1.00	1	0.50	* Refl. < -20 dB
Field Probe Calibration	0.21	Tolerance	N	1.00	1	0.21	
Field Probe Isotropy	0.01	Tolerance	N	1.00	1	0.01	
Field Probe Frequency Response	0.135	Tolerance	N	1.00	1	0.14	
Field Probe Linearity	0.013	Tolerance	N	1.00	1	0.01	
Modulation Interference Factor	0.20	Tolerance	R	1.73	1	0.12	Applicable for M-rating testing
Boundary Effects	0.105	Accuracy	R	1.73	1	0.06	*
Probe Positioning Accuracy	0.20	Accuracy	R	1.73	1	0.12	*
Probe Positioner	0.050	Accuracy	R	1.73	1	0.03	*
Extrapolation/Interpolation	0.045	Tolerance	R	1.73	1	0.03	*
Resolution to 2mm error	0.21	Tolerance	N	1.00	1	0.21	
System Detection Limit	0.05	Tolerance	R	1.73	1	0.03	*
Readout Electronics	0.015	Tolerance	N	1.00	1	0.02	*
Integration Time	0.11	Tolerance	R	1.73	1	0.06	*
Response Time	0.033	Tolerance	R	1.73	1	0.02	*
Phantom Thickness	0.10	Tolerance	R	1.73	1	0.06	*
System Repeatability (Field x 2=power)	0.17	Tolerance	N	1.00	1	0.17	*
Test Sample Related							
Device Positioning Vertical	0.2	Tolerance	R	1.73	1	0.12	*
Device Positioning Lateral	0.045	Tolerance	R	1.73	1	0.03	*
Device Holder and Phantom	0.1	Tolerance	R	1.73	1	0.06	*
Power Drift	0.21	Tolerance	R	1.73	1	0.12	
Combined Standard Uncertainty (k=1)						0.66	16.3%
Expanded Uncertainty [95% confidence]					1.31	32.6%	
Expanded Uncertainty [95% confidence] on Field					0.66	16.3%	

Notes:

- Test equipments are calibrated according to techniques outlined in NIS81, NIS3003 and NIST Tech Note 1297, All equipments have traceability according to NIST. Measurement Uncertainties are defined in further detail in NIS 81 and NIST Tech Note 1297 and UKAS M3003.
- 2. * Uncertainty specifications from Schmidt & Partner Engineering AG (not site specific)

Measurement uncertainty reflects the quality and accuracy of a measured result as compared to the true value. Such statements are generally required when stating results of measurements so that it is clear to the intended audience that the results may differ when reproduced by different facilities. Measurement results vary due to the measurement uncertainty of the instrumentation, measurement technique, and test engineer. Most uncertainties are calculated using the tolerances of the instrumentation used in the measurement, the measurement setup variability, and the technique used in performing the test. While not generally included, the variability of the equipment under test also figures into the overall measurement uncertainty. Another component of the overall uncertainty is based on the variability of repeated measurements (so-called Type A uncertainty). This may mean that the Hearing Aid immunity tests may have to be repeated by taking down the test setup and resetting it up so that there are a statistically significant number of repeat measurements to identify the measurement uncertainty. By combining the repeat measurement results with that of the instrumentation chain using the technique contained in NIS 81 and NIS 3003, the overall measurement uncertainty was estimated.

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13. TEST DATA

See following Attached Pages for Test Data.

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DUT: CD835V3 - SN1082

Type: CD835V3 Serial: 1082

Communication System: CW; Frequency: 835 MHz;

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

DASY5 Configuration:

- Probe: ER3DV6 SN2335; Calibrated: 8/11/2017;
- · Sensor-Surface: 0mm (Fix Surface)
- Electronics: DAE4 Sn859; Calibrated: 5/17/2017
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY52, Version 52.10 (0);

835 MHz / 100mW HAC Dipole Validation at 15mm/Hearing Aid Compatibility Test (41x361x1):

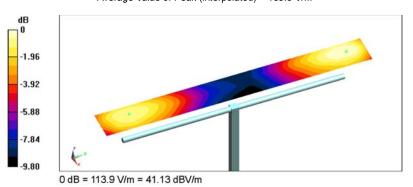
Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 110.6 V/m; Power Drift = 0.15 dB

Applied MIF = 0.00 dB

Average Value of Peak (interpolated) = 109.9 V/m



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DUT: CD1880V3 - SN1064

Type: CD1880V3 Serial: 1064

Communication System: CW; Frequency: 1880 MHz;

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

DASY5 Configuration:

- Probe: ER3DV6 SN2335; Calibrated: 8/11/2017;
- · Sensor-Surface: 0mm (Fix Surface)
- Electronics: DAE4 Sn859; Calibrated: 5/17/2017
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY52, Version 52.10 (0);

1880 MHz / 100mW HAC Dipole Validation at 15mm/Hearing Aid Compatibility Test (41x181x1):

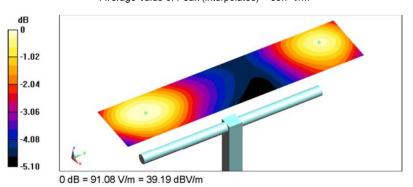
Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 150.9 V/m; Power Drift = 0.04 dB

Applied MIF = 0.00 dB

Average Value of Peak (interpolated) = 89.7 V/m



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Type: Portable Handset Serial: 18253 Backlight off Duty Cycle: 1:8

Communication System: CDMA; Frequency: 836.52 MHz;

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

DASY5 Configuration:

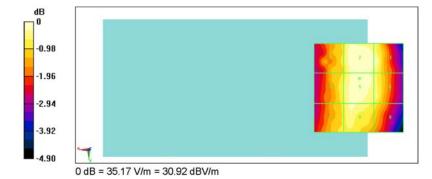
- Probe: ER3DV6 SN2335; Calibrated: 8/11/2017;
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn859; Calibrated: 5/17/2017
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY52, Version 52.10 (0);

Cell. CDMA Mid Channel / Hearing Aid Compatibility Test (101x101x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 31.35 V/m; Power Drift = -0.04 dB Applied MIF = 3.09 dB RF audio interference level = 30.92 dBV/m Emission category: M4

MIF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
30.15 dBV/m	30.91 dBV/m	30.8 dBV/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
30.32 dBV/m	30.92 dBV/m	30.53 dBV/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
30.15 dBV/m	30 71 dBV/m	30.21 dBV/m



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Type: Portable Handset Serial: 18253 Backlight off Duty Cycle: 1:8

Communication System: CDMA; Frequency: 1851.25 MHz;

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

DASY5 Configuration:

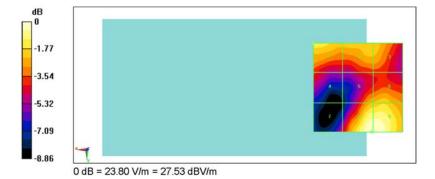
- Probe: ER3DV6 SN2335; Calibrated: 8/11/2017;
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn859; Calibrated: 5/17/2017
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY52, Version 52.10 (0);

PCS CDMA Low Channel / Hearing Aid Compatibility Test (101x101x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 9.643 V/m; Power Drift = 0.13 dB Applied MIF = 3.05 dB RF audio interference level = 27.38 dBV/m Emission category: M4

MIF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
26.49 dBV/m	25.67 dBV/m	25.65 dBV/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
23.68 dBV/m	25.23 dBV/m	25.65 dBV/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
23 dBV/m	27.38 dBV/m	27.38 dBV/m



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Type: Portable Handset Serial: 18253 Backlight off Duty Cycle: 1:8.3

Communication System: GSM; Frequency: 836.6 MHz;

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

DASY5 Configuration:

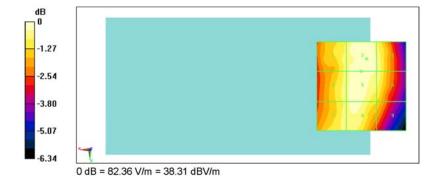
- Probe: ER3DV6 SN2335; Calibrated: 8/11/2017;
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn859; Calibrated: 5/17/2017
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY52, Version 52.10 (0);

GSM850 Mid Channel / Hearing Aid Compatibility Test (101x101x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 66.67 V/m; Power Drift = 0.18 dB Applied MIF = 3.56 dB RF audio interference level = 38.38 dBV/m Emission category: M4

MIF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
37.7 dBV/m	38.38 dBV/m	37.9 dBV/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
37.78 dBV/m	38.23 dBV/m	37.85 dBV/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
37.71 dBV/m	38.1 dBV/m	37.07 dBV/m



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Type: Portable Handset Serial: 18253 Backlight off Duty Cycle: 1:8.3

Communication System: GSM; Frequency: 1909.8 MHz;

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

DASY5 Configuration:

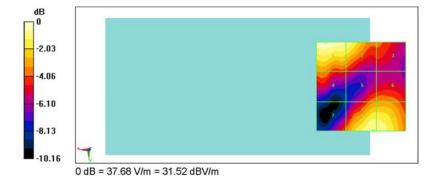
- Probe: ER3DV6 SN2335; Calibrated: 8/11/2017;
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn859; Calibrated: 5/17/2017
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY52, Version 52.10 (0);

GSM1900 High Channel / Hearing Aid Compatibility Test (101x101x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 15.22 V/m; Power Drift = -0.13 dB Applied MIF = 3.56 dB RF audio interference level = 31.58 dBV/m Emission category: M3

MIF scaled E-field

Grid 1 M3	Grid 2 M3	Grid 3 M4
31.58 dBV/m	30.86 dBV/m	27.74 dBV/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
28.25 dBV/m	28.16 dBV/m	28.3 dBV/m
Grid 7 M4	Grid 8 M3	Grid 9 M3



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14. CALIBRATION CERTIFICATES

The following pages include the probe calibration used to evaluate HAC for the DUT.

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Calibration Laboratory of Schmid & Partner Engineering AG Zeughausstrasse 43, 8004 Zurich, Switzerland





С

Schweizerischer Kalibrierdienst Service suisse d'étalonnage Servizio svizzero di taratura Swiss Calibration Service

Accredited by the Swiss Accreditation Service (SAS)
The Swiss Accreditation Service is one of the signatories to the EA
Multilateral Agreement for the recognition of calibration certificates

Accreditation No.: SCS 0108

Client

PC Test

Certificate No: ER3-2335_Aug17

CALIBRATION CERTIFICATE

Object

ER3DV6 - SN:2335

Calibration procedure(s)

QA CAL-02.v8, QA CAL-25.v6

Calibration procedure for E-field probes optimized for close near field

evaluations in air

Calibration date:

August 11, 2017

This calibration certificate documents the traceability to national standards, which realize the physical units of measurements (SI).
The measurements and the uncertainties with confidence probability are given on the following pages and are part of the certificate.

All calibrations have been conducted in the closed laboratory facility: environment temperature (22 ± 3)°C and humidity < 70%.

Calibration Equipment used (M&TF critical for calibration)

/OA 08/30/2017

Primary Standards	ID	Cal Date (Certificate No.)	Scheduled Calibration
Power meter NRP	SN: 104778	04-Apr-17 (No. 217-02521/02522)	Apr-18
Power sensor NRP-Z91	SN: 103244	04-Apr-17 (No. 217-02521)	Apr-18
Power sensor NRP-Z91	SN: 103245	04-Apr-17 (No. 217-02525)	Apr-18
Reference 20 dB Attenuator	SN: S5277 (20x)	07-Apr-17 (No. 217-02528)	Apr-18
Reference Probe ER3DV6	SN: 2328	14-Oct-16 (No. ER3-2328_Oct16)	Oct-17
DAE4	SN: 789	2-Aug-17 (No. DAE4-789_Aug17)	Aug-18
Secondary Standards	ID	Check Date (in house)	Scheduled Check
Power meter E4419B	SN: GB41293874	06-Apr-16 (in house check Jun-16)	In house check: Jun-18
Power sensor E4412A	SN: MY41498087	06-Apr-16 (in house check Jun-16)	In house check: Jun-18
Power sensor E4412A	SN: 000110210	06-Apr-16 (in house check Jun-16)	In house check: Jun-18
RF generator HP 8648C	SN: US3642U01700	04-Aug-99 (in house check Jun-16)	In house check: Jun-18
Network Analyzer HP 8753E	SN: US37390585	18-Oct-01 (in house check Oct-16)	In house check: Oct-17

Issued: August 12, 201

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Certificate No: ER3-2335_Aug17

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FCC ID: A3LSMJ337V	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 45 of 72
1M1803190049-09-R1.A3L	04/09/2018 - 04/13/2018	Portable Handset		raye 45 01 72

Calibration Laboratory of Schmid & Partner Engineering AG Zeughausstrasse 43, 8004 Zurich, Switzerland





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Accreditation No.: SCS 0108

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Glossary:

NORMx,y,z sensitivity in free space diode compression point

CF crest factor (1/duty_cycle) of the RF signal modulation dependent linearization parameters

Polarization φ φ rotation around probe axis

Polarization 9 9 rotation around an axis that is in the plane normal to probe axis (at measurement center),

i.e., $\vartheta = 0$ is normal to probe axis

Connector Angle information used in DASY system to align probe sensor X to the robot coordinate system

Calibration is Performed According to the Following Standards:

 IEEE Std 1309-2005, "IEEE Standard for calibration of electromagnetic field sensors and probes, excluding antennas, from 9 kHz to 40 GHz", December 2005

b) CTIA Test Plan for Hearing Aid Compatibility, Rev 3.0, November 2013

Methods Applied and Interpretation of Parameters:

- NORMx,y,z: Assessed for E-field polarization 9 = 0 for XY sensors and 9 = 90 for Z sensor (f ≤ 900 MHz in TEM-cell; f > 1800 MHz: R22 waveguide).
- NORM(f)x,y,z = NORMx,y,z * frequency_response (see Frequency Response Chart).
- DCPx,y,z: DCP are numerical linearization parameters assessed based on the data of power sweep with CW signal (no uncertainty required). DCP does not depend on frequency nor media.
- PAR: PAR is the Peak to Average Ratio that is not calibrated but determined based on the signal characteristics
- Ax,y,z; Bx,y,z; Cx,y,z; Dx,y,z; VRx,y,z: A, B, C, D are numerical linearization parameters assessed based on the data of power sweep for specific modulation signal. The parameters do not depend on frequency nor media. VR is the maximum calibration range expressed in RMS voltage across the diode.
- Spherical isotropy (3D deviation from isotropy): in a locally homogeneous field realized using an open waveguide setup.
- Sensor Offset: The sensor offset corresponds to the offset of virtual measurement center from the probe tip (on probe axis). No tolerance required.
- Connector Angle: The angle is assessed using the information gained by determining the NORMx (no uncertainty required).

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ER3DV6 ~ SN:2335 August 11, 2017

Probe ER3DV6

SN:2335

Manufactured: Calibrated:

September 9, 2003 August 11, 2017

Calibrated for DASY/EASY Systems (Note: non-compatible with DASY2 system!)

Certificate No: ER3-2335_Aug17

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ER3DV6 - SN:2335 August 11, 2017

DASY/EASY - Parameters of Probe: ER3DV6 - SN:2335

Basic Calibration Parameters

	Sensor X	Sensor Y	Sensor Z	Unc (k=2)
Norm $(\mu V/(V/m)^2)$	1.61	1.64	1.83	± 10.1 %
DCP (mV) ^B	99.3	98.5	100.0	

Modulation Calibration Parameters

UID	Communication System Name		A dB	B dB√μV	С	D dB	VR mV	Unc ^E (k=2)
0	CW	X	0.0	0.0	1.0	0.00	194.5	±3.8 %
		Υ	0.0	0.0	1.0		207.3	
		Z	0.0	0.0	1.0		191.6	

The reported uncertainty of measurement is stated as the standard uncertainty of measurement multiplied by the coverage factor k=2, which for a normal distribution corresponds to a coverage probability of approximately 95%.

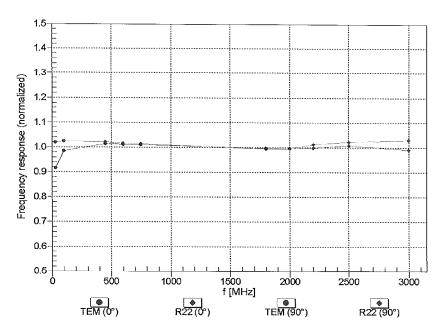
Certificate No: ER3-2335_Aug17

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FCC ID: A3LSMJ337V	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
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⁸ Numerical linearization parameter: uncertainty not required.
^E Uncertainty is determined using the max. deviation from linear response applying rectangular distribution and is expressed for the square of the field value.

Frequency Response of E-Field (TEM-Cell:ifi110 EXX, Waveguide: R22)



Uncertainty of Frequency Response of E-field: ± 6.3% (k=2)

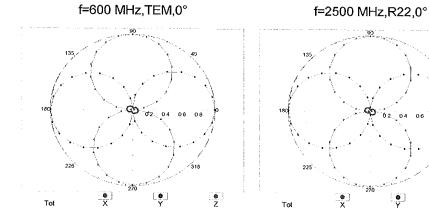
Certificate No: ER3-2335_Aug17

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FCC ID: A3LSMJ337V	CONTEST HA	HAC (RF EMISSIONS) TEST REPORT		Approved by: Quality Manager
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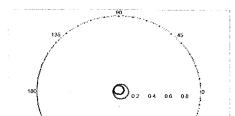
ER3DV6 -- SN:2335 August 11, 2017

Receiving Pattern (ϕ), $\vartheta = 0^{\circ}$



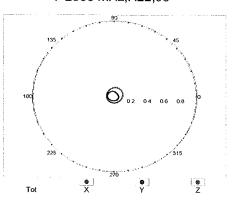
Receiving Pattern (ϕ), $\vartheta = 90^{\circ}$

f=600 MHz,TEM,90°



f=2500 MHz,R22,90°

⊗ Z



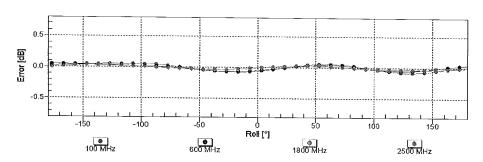
Certificate No: ER3-2335_Aug17

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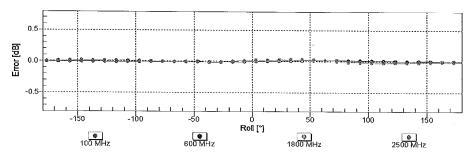
FCC ID: A3LSMJ337V	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
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Receiving Pattern (ϕ), $\vartheta = 0^{\circ}$



Uncertainty of Axial Isotropy Assessment: ± 0.5% (k=2)

Receiving Pattern (ϕ), $\vartheta = 90^{\circ}$



Uncertainty of Axial Isotropy Assessment: ± 0.5% (k=2)

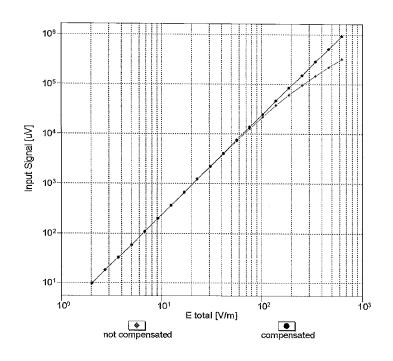
Certificate No: ER3-2335_Aug17

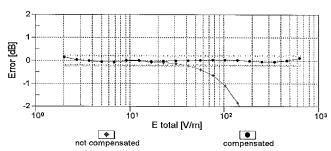
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ER3DV6 - SN:2335 August 11, 2017

Dynamic Range f(E-field) (TEM cell , f = 900 MHz)





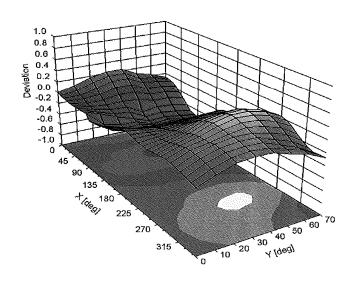
Uncertainty of Linearity Assessment: ± 0.6% (k=2)

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FCC ID: A3LSMJ337V	PCTEST: HA	HAC (RF EMISSIONS) TEST REPORT		Approved by: Quality Manager
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Deviation from Isotropy in Air

Error (φ, ϑ), f = 900 MHz



-1.0 -0.8 -0.6 -0.4 -0.2 0.0 0.2 0.4 0.6 0.8 1.0

Uncertainty of Spherical Isotropy Assessment: ± 2.6% (k=2)

Certificate No: ER3-2335_Aug17

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ER3DV6 - SN:2335 August 11, 2017

DASY/EASY - Parameters of Probe: ER3DV6 - SN:2335

Other Probe Parameters

Sensor Arrangement	Rectangular
Connector Angle (°)	83.1
Mechanical Surface Detection Mode	enabled
Optical Surface Detection Mode	disabled
Probe Overall Length	337 mm
Probe Body Diameter	10 mm
Tip Length	10 mm
Tip Diameter	8 mm
Probe Tip to Sensor X Calibration Point	2.5 mm
Probe Tip to Sensor Y Calibration Point	2.5 mm
Probe Tip to Sensor Z Calibration Point	2.5 mm

Certificate No: ER3-2335_Aug17

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FCC ID: A3LSMJ337V	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
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Accreditation No.: SCS 0108

Client PC Test

Certificate No: CD835V3-1082 May16

CALIBRATION CERTIFICATE Object CD835V3 - SN: 1082 Calibration procedure(s) QA CAL-20.v6 Calibration procedure for dipoles in air Calibration date: May 10, 2016 This calibration certificate documents the traceability to national standards, which realize the physical units of measurements (SI). The measurements and the uncertainties with confidence probability are given on the following pages and are part of the certificate. All calibrations have been conducted in the closed laboratory facility: environment temperature (22 ± 3)°C and humidity < 70%. Calibration Equipment used (M&TE critical for calibration) Primary Standards ID# Cal Date (Certificate No.) Scheduled Calibration Power meter NRP SN: 104778 06-Apr-16 (No. 217-02288/02289) Apr-17 Power sensor NRP-Z91 SN: 103244 06-Apr-16 (No. 217-02288) Apr-17 Power sensor NRP-Z91 SN: 103245 06-Apr-16 (No. 217-02289) Apr-17 Reference 20 dB Attenuator SN: 5058 (20k) 05-Apr-16 (No. 217-02292) Apr-17 Type-N mismatch combination SN: 5047.2 / 06327 05-Apr-16 (No. 217-02295) Apr-17 Probe ER3DV6 SN: 2336 31-Dec-15 (No. ER3-2336_Dec15) Dec-16 Probe H3DV6 SN: 6065 31-Dec-15 (No. H3-6065_Dec15) Dec-16 DAE4 SN: 781 04-Sep-15 (No. DAE4-781_Sep15) Sep-16 Secondary Standards ID# Check Date (in house) Scheduled Check Power meter Agilent 4419B SN: GB42420191 09-Oct-09 (in house check Sep-14) In house check: Oct-17 Power sensor HP E4412A SN: US38485102 05-Jan-10 (in house check Sep-14) In house check: Oct-17 Power sensor HP 8482A SN: US37295597 09-Oct-09 (in house check Sep-14) In house check: Oct-17 RF generator R&S SMT-06 SN: 832283/011 27-Aug-12 (in house check Oct-15) In house check: Oct-17 Network Analyzer HP 8753E SN: US37390585 18-Oct-01 (in house check Oct-15) In house check: Oct-16 Name Function Calibrated by: Jeton Kastrati Laboratory Technician Approved by: Katja Pokovic Technical Manager Issued: May 12, 2016 This calibration certificate shall not be reproduced except in full without written approval of the laboratory.

Certificate No: CD835V3-1082_May16

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FCC ID: A3LSMJ337V	PCTEST	HAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
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References

ANSI-C63.19-2011
 American National Standard, Methods of Measurement of Compatibility between Wireless Communications
 Devices and Hearing Aids.

Methods Applied and Interpretation of Parameters:

- Coordinate System: y-axis is in the direction of the dipole arms. z-axis is from the basis of the antenna
 (mounted on the table) towards its feed point between the two dipole arms. x-axis is normal to the other axes.
 In coincidence with the standards [1], the measurement planes (probe sensor center) are selected to be at a
 distance of 15 mm above the top metal edge of the dipole arms.
- Measurement Conditions: Further details are available from the hardcopies at the end of the certificate. All
 figures stated in the certificate are valid at the frequency indicated. The forward power to the dipole connector
 is set with a calibrated power meter connected and monitored with an auxiliary power meter connected to a
 directional coupler. While the dipole under test is connected, the forward power is adjusted to the same level.
- Antenna Positioning: The dipole is mounted on a HAC Test Arch phantom using the matching dipole positioner with the arms horizontal and the feeding cable coming from the floor. The measurements are performed in a shielded room with absorbers around the setup to reduce the reflections. It is verified before the mounting of the dipole under the Test Arch phantom, that its arms are perfectly in a line. It is installed on the HAC dipole positioner with its arms parallel below the dielectric reference wire and able to move elastically in vertical direction without changing its relative position to the top center of the Test Arch phantom. The vertical distance to the probe is adjusted after dipole mounting with a DASYS Surface Check job. Before the measurement, the distance between phantom surface and probe tip is verified. The proper measurement distance is selected by choosing the matching section of the HAC Test Arch phantom with the proper device reference point (upper surface of the dipole) and the matching grid reference point (tip of the probe) considering the probe sensor offset. The vertical distance to the probe is essential for the accuracy.
- Feed Point Impedance and Return Loss: These parameters are measured using a HP 8753E Vector Network Analyzer. The impedance is specified at the SMA connector of the dipole. The influence of reflections was eliminating by applying the averaging function while moving the dipole in the air, at least 70cm away from any obstacles.
- E-field distribution: E field is measured in the x-y-plane with an isotropic ER3D-field probe with 100 mW forward power to the antenna feed point. In accordance with [1], the scan area is 20mm wide, its length exceeds the dipole arm length (180 or 90mm). The sensor center is 15 mm (in z) above the metal top of the dipole arms. Two 3D maxima are available near the end of the dipole arms. Assuming the dipole arms are perfectly in one line, the average of these two maxima (in subgrid 2 and subgrid 8) is determined to compensate for any non-parallelity to the measurement plane as well as the sensor displacement. The E-field value stated as calibration value represents the maximum of the interpolated 3D-E-field, in the plane above the dipole surface.

The reported uncertainty of measurement is stated as the standard uncertainty of measurement multiplied by the coverage factor k=2, which for a normal distribution corresponds to a coverage probability of approximately 95%.

Certificate No: CD835V3-1082_May16 Page 2 of 5

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Measurement Conditions

DASY system configuration, as far as not given on page 1.

DASY Version	DASY5	V52.8.8
Phantom	HAC Test Arch	
Distance Dipole Top - Probe Center	15 mm	
Scan resolution	dx, dy = 5 mm	
Frequency	835 MHz ± 1 MHz	
Input power drift	< 0.05 dB	

Maximum Field values at 835 MHz

E-field 15 mm above dipole surface	re dipole surface condition	
Maximum measured above high end	100 mW input power	107.5 V/m = 40.63 dBV/m
Maximum measured above low end	100 mW input power	106.1 V/m = 40.51 dBV/m
Averaged maximum above arm	100 mW input power	106.8 V/m ± 12.8 % (k=2)

Appendix (Additional assessments outside the scope of SCS 0108)

Antenna Parameters

Frequency	Return Loss	Impedance 44.5 Ω - 13.4 jΩ	
800 MHz	16.4 dB		
835 MHz	26.3 dB	50.0 Ω + 4.9 jΩ	
900 MHz	16.4 dB	57.4 Ω - 14.7 jΩ	
950 MHz	21.9 dB	43.6 Ω + 4.0 jΩ	
960 MHz	17.2 dB	47.9 Ω + 13.5 jΩ	

3.2 Antenna Design and Handling

The calibration dipole has a symmetric geometry with a built-in two stub matching network, which leads to the enhanced bandwidth.

The dipole is built of standard semirigid coaxial cable. The internal matching line is open ended. The antenna is therefore open for DC signals.

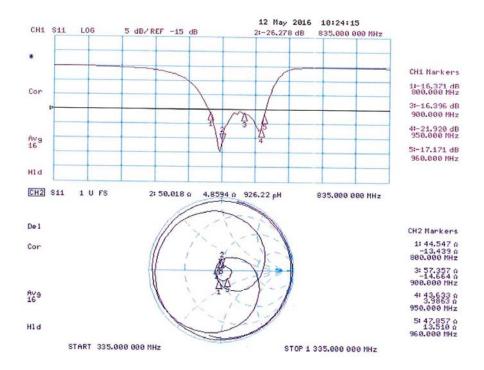
Do not apply force to dipole arms, as they are liable to bend. The soldered connections near the feedpoint may be damaged. After excessive mechanical stress or overheating, check the impedance characteristics to ensure that the internal matching network is not affected.

After long term use with 40W radiated power, only a slight warming of the dipole near the feedpoint can be measured.

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Impedance Measurement Plot



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DASY5 E-field Result

Date: 10.05.2016

Test Laboratory: SPEAG Lab2

DUT: HAC-Dipole 835 MHz; Type: CD835V3; Serial: CD835V3 - SN: 1082

Communication System: UID 0 - CW ; Frequency: 835 MHz Medium parameters used: $\sigma=0$ S/m, $\epsilon_r=1$; $\rho=1000$ kg/m 3 Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

DASY52 Configuration:

- Probe: ER3DV6 SN2336; ConvF(1, 1, 1); Calibrated: 31.12.2015;
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn781; Calibrated: 04.09.2015
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1070
- DASY52 52.8.8(1258); SEMCAD X 14.6.10(7372)

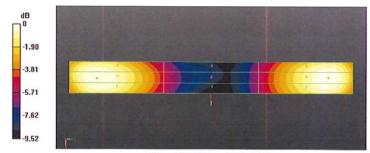
Dipole E-Field measurement @ 835MHz/E-Scan - 835MHz d=15mm/Hearing Aid Compatibility Test (41x361x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm Reference Value = 109.8 V/m; Power Drift = 0.02 dB Applied MIF = 0.00 dBRF audio interference level = 40.63 dBV/m

Emission category: M3

MIF scaled E-field

Grid 1 M3 40.52 dBV/m	The second section of the property of	Grid 3 M3 40.46 dBV/m
Grid 4 M4 35.69 dBV/m		
Grid 7 M3 40.38 dBV/m		Grid 9 M3 40.37 dBV/m



0 dB = 107.5 V/m = 40.63 dBV/m

Certificate No: CD835V3-1082_May16

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FCC ID: A3LSMJ337V	PCTEST	HAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
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Accreditation No.: SCS 0108

Client

PC Test

Certificate No: CD1880V3-1064_May16

CALIBRATION CERTIFICATE Object CD1880V3 - SN: 1064 Calibration procedure(s) QA CAL-20.v6 Calibration procedure for dipoles in air Calibration date: May 12, 2016 This calibration certificate documents the traceability to national standards, which realize the physical units of measurements (SI). The measurements and the uncertainties with confidence probability are given on the following pages and are part of the certificate. All calibrations have been conducted in the closed laboratory facility: environment temperature (22 ± 3)°C and humidity < 70%. Calibration Equipment used (M&TE critical for calibration) Primary Standards Cal Date (Certificate No.) Scheduled Calibration Power meter NRP SN: 104778 06-Apr-16 (No. 217-02288/02289) Apr-17 Power sensor NRP-Z91 SN: 103244 06-Apr-16 (No. 217-02288) Apr-17 Power sensor NRP-Z91 SN: 103245 06-Apr-16 (No. 217-02289) Apr-17 Reference 20 dB Attenuator SN: 5058 (20k) 05-Apr-16 (No. 217-02292) Apr-17 Type-N mismatch combination SN: 5047.2 / 06327 05-Apr-16 (No. 217-02295) Apr-17 Probe ER3DV6 SN: 2336 31-Dec-15 (No. ER3-2336_Dec15) Probe H3DV6 SN: 6065 31-Dec-15 (No. H3-6065_Dec15) Dec-16 DAE4 SN: 781 04-Sep-15 (No. DAE4-781_Sep15) Sep-16 Secondary Standards ID# Check Date (in house) Scheduled Check Power meter Agilent 4419B SN: GB42420191 09-Oct-09 (in house check Sep-14) In house check: Oct-17 Power sensor HP E4412A SN: US38485102 05-Jan-10 (in house check Sep-14) In house check: Oct-17 Power sensor HP 8482A SN: US37295597 09-Oct-09 (in house check Sep-14) In house check: Oct-17 RF generator R&S SMT-06 SN: 832283/011 27-Aug-12 (in house check Oct-15) In house check: Oct-17 Network Analyzer HP 8753E SN: US37390585 18-Oct-01 (in house check Oct-15) In house check: Oct-16 Function Signature Calibrated by: Jeton Kastrati Laboratory Technician Katja Pokovic Approved by: Technical Manager Issued: May 12, 2016 This calibration certificate shall not be reproduced except in full without written approval of the laboratory.

Certificate No: CD1880V3-1064_May16

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Schweizerischer Kalibrierdienst Service sulsse d'étalonnage Servizio svizzero di taratura Swiss Calibration Service

Accreditation No.: SCS 0108

Accredited by the Swiss Accreditation Service (SAS)

The Swiss Accreditation Service is one of the signatories to the EA

Multilateral Agreement for the recognition of calibration certificates

References

[1] ANSI-C63.19-2011

American National Standard, Methods of Measurement of Compatibility between Wireless Communications Devices and Hearing Aids.

Methods Applied and Interpretation of Parameters:

- Coordinate System: y-axis is in the direction of the dipole arms. z-axis is from the basis of the antenna
 (mounted on the table) towards its feed point between the two dipole arms. x-axis is normal to the other axes.
 In coincidence with the standards [1], the measurement planes (probe sensor center) are selected to be at a
 distance of 15 mm above the top metal edge of the dipole arms.
- Measurement Conditions: Further details are available from the hardcopies at the end of the certificate. All
 figures stated in the certificate are valid at the frequency indicated. The forward power to the dipole connector
 is set with a calibrated power meter connected and monitored with an auxiliary power meter connected to a
 directional coupler. While the dipole under test is connected, the forward power is adjusted to the same level.
- Antenna Positioning: The dipole is mounted on a HAC Test Arch phantom using the matching dipole positioner with the arms horizontal and the feeding cable coming from the floor. The measurements are performed in a shielded room with absorbers around the setup to reduce the reflections. It is verified before the mounting of the dipole under the Test Arch phantom, that its arms are perfectly in a line. It is installed on the HAC dipole positioner with its arms parallel below the dielectric reference wire and able to move elastically in vertical direction without changing its relative position to the top center of the Test Arch phantom. The vertical distance to the probe is adjusted after dipole mounting with a DASY5 Surface Check job. Before the measurement, the distance between phantom surface and probe tip is verified. The proper measurement distance is selected by choosing the matching section of the HAC Test Arch phantom with the proper device reference point (upper surface of the dipole) and the matching grid reference point (tip of the probe) considering the probe sensor offset. The vertical distance to the probe is essential for the accuracy.
- Feed Point Impedance and Return Loss: These parameters are measured using a HP 8753E Vector Network Analyzer. The impedance is specified at the SMA connector of the dipole. The influence of reflections was eliminating by applying the averaging function while moving the dipole in the air, at least 70cm away from any obstacles.
- E-field distribution: E field is measured in the x-y-plane with an isotropic ER3D-field probe with 100 mW forward power to the antenna feed point. In accordance with [1], the scan area is 20mm wide, its length exceeds the dipole arm length (180 or 90mm). The sensor center is 15 mm (in z) above the metal top of the dipole arms. Two 3D maxima are available near the end of the dipole arms. Assuming the dipole arms are perfectly in one line, the average of these two maxima (in subgrid 2 and subgrid 8) is determined to compensate for any non-parallelity to the measurement plane as well as the sensor displacement. The E-field value stated as calibration value represents the maximum of the interpolated 3D-E-field, in the plane above the dipole surface.

The reported uncertainty of measurement is stated as the standard uncertainty of measurement multiplied by coverage factor k=2, which for a normal distribution corresponds to a coverage probability of approximately stated as the standard uncertainty of measurement multiplied by coverage factor k=2, which for a normal distribution corresponds to a coverage probability of approximately stated as the standard uncertainty of measurement multiplied by coverage factor k=2, which for a normal distribution corresponds to a coverage probability of approximately stated as the standard uncertainty of measurement multiplied by coverage factor k=2, which for a normal distribution corresponds to a coverage probability of approximately stated as the standard uncertainty of measurement multiplied by coverage factor k=2, which for a normal distribution corresponds to a coverage probability of approximately stated as the standard uncertainty of the standard		
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Measurement Conditions

DASY system configuration, as far as not given on page 1.

DASY Version	DASY5	V52.8.8
Phantom	HAC Test Arch	
Distance Dipole Top - Probe Center	15 mm	
Scan resolution	dx, dy = 5 mm	
Frequency	1730 MHz ± 1 MHz 1880 MHz ± 1 MHz	
Input power drift	< 0.05 dB	

Maximum Field values at 1730 MHz

E-field 15 mm above dipole surface	condition	Interpolated maximum
Maximum measured above high end	100 mW input power	96.1 V/m = 39.66 dBV/m
Maximum measured above low end	100 mW input power	95.3 V/m = 39.58 dBV/m
Averaged maximum above arm	100 mW input power	95.7 V/m ± 12.8 % (k=2)

Maximum Field values at 1880 MHz

E-field 15 mm above dipole surface	condition	Interpolated maximum
Maximum measured above high end	100 mW input power	91.2 V/m = 39.20 dBV/m
Maximum measured above low end	100 mW input power	88.0 V/m = 38.89 dBV/m
Averaged maximum above arm	100 mW input power	89.6 V/m ± 12.8 % (k=2)

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Appendix (Additional assessments outside the scope of SCS 0108)

Antenna Parameters

Nominal Frequencies

Frequency	Return Loss	Impedance
1730 MHz	24.0 dB	$49.6 \Omega + 6.3 jΩ$
1880 MHz	19.8 dB	49.5 Ω + 10.2 jΩ
1900 MHz	20.4 dB	52.9 Ω + 9.4 jΩ
1950 MHz	26.8 dB	54.4 Ω + 1.8 jΩ
2000 MHz	22.7 dB	$43.2 \Omega + 0.8 j\Omega$

3.2 Antenna Design and Handling

The calibration dipole has a symmetric geometry with a built-in two stub matching network, which leads to the enhanced bandwidth.

The dipole is built of standard semirigid coaxial cable. The internal matching line is open ended. The antenna is therefore open for DC signals.

Do not apply force to dipole arms, as they are liable to bend. The soldered connections near the feedpoint may be damaged. After excessive mechanical stress or overheating, check the impedance characteristics to ensure that the internal matching network is not affected.

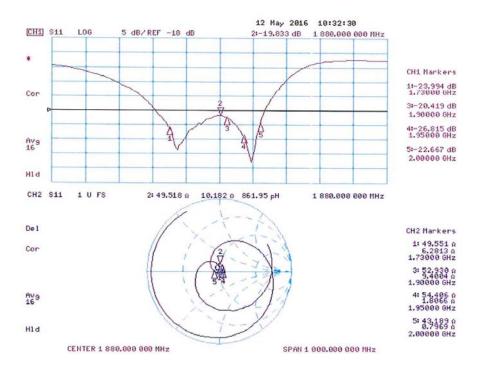
After long term use with 40W radiated power, only a slight warming of the dipole near the feedpoint can be measured.

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Impedance Measurement Plot



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DASY5 E-field Result

Date: 10.05.2016

Test Laboratory: SPEAG Lab2

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: CD1880V3 - SN: 1064

Communication System: UID 0 - CW ; Frequency: 1880 MHz, Frequency: 1730 MHz Medium parameters used: $\sigma=0$ S/m, $\epsilon_r=1$; $\rho=1000$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

DASY52 Configuration:

- Probe: ER3DV6 SN2336; ConvF(1, 1, 1); Calibrated: 31.12.2015;
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn781; Calibrated: 04.09.2015
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1070
- DASY52 52.8.8(1258); SEMCAD X 14.6.10(7372)

Dipole E-Field measurement @ 1880MHz/E-Scan - 1880MHz d=15mm/Hearing Aid Compatibility Test (41x181x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm Reference Value = 151.7 V/m; Power Drift = -0.01 dB Applied MIF = 0.00 dB

RF audio interference level = 39.20 dBV/m Emission category: M2

MIF scaled E-field

Grid 1 M2 39.04 dBV/m		Grid 3 M2 39.08 dBV/m
Grid 4 M2 36.76 dBV/m		Grid 6 M2 36.75 dBV/m
Grid 7 M2 38.68 dBV/m	CONTRACTOR OF PROPERTY.	Grid 9 M2 38.8 dBV/m

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Dipole E-Field measurement @ 1880MHz/E-Scan - 1730MHz d=15mm/Hearing Aid Compatibility Test (41x181x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 168.3 V/m; Power Drift = 0.00 dB

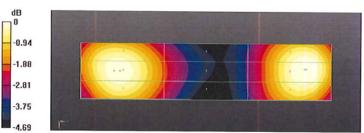
Applied MIF = 0.00 dB

RF audio interference level = 39.66 dBV/m

Emission category: M2

MIF scaled E-field

Grid 1 M2 39.43 dBV/m		
Grid 4 M2 37.46 dBV/m	Grid 5 M2 37.56 dBV/m	
	Grid 8 M2 39.66 dBV/m	



0 dB = 91.23 V/m = 39.20 dBV/m

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15. CONCLUSION

The measurements taken in accordance with the procedures provided in the CTIA Test Plan for Hearing Aid Compatibility Rev 3.1, February 2017, indicate that the wireless communications device complies with the HAC limits specified in the ANSI C63.19 Standard and FCC WT Docket No. 01-309 RM-8658. Precise laboratory measures were taken to assure repeatability of the tests. The tested device complies with the requirements in respect to all parameters specific to the test. The test results and statements relate only to the item(s) tested.

Please note that the M-rating for this equipment only represents the field interference possible against a hypothetical and typical hearing aid. The measurement system and techniques presented in this evaluation are proposed in the ANSI standard as a means of best approximating wireless device compatibility with a hearing-aid. The literature is under continual re-construction.

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